

# **APPLICATIONS OF LOW TEMPERATURE PLASMAS: STATUS, SCIENTIFIC ISSUES AND OPPORTUNITIES\***

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- **Contributing Group Members**

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- **Ananth Bhoj**
- **Ankur Agarwal**
- **Alex Vasenkov**

- **Provided Materials and Insights:**

- **Eray Aydil**
- **Kurt Becker**
- **Matt Blain**
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- **Fred Huang**
- **Uwe Kortshagen**
- **D. Manos**
- **T. Mantei**
- **Louis Rosocha**
- **P. Schenborn**
- **Karen Seward**
- **Tim Sommerer**
- **Peter Ventzek**
- **David Wharmby**

# AGENDA

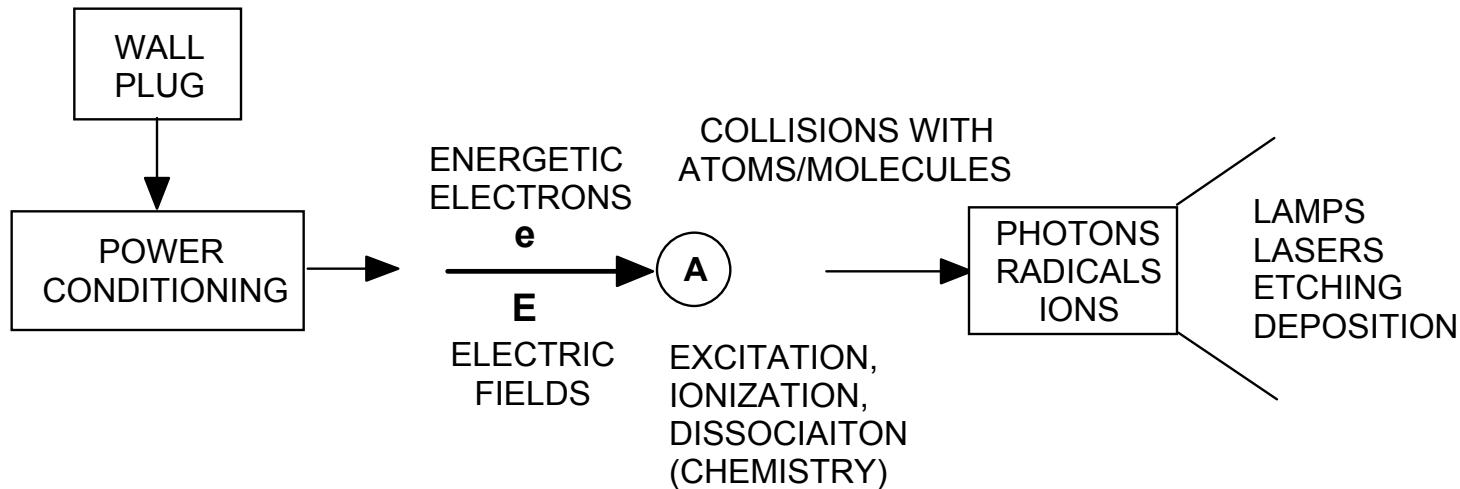
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- **Applications of Low Temperature Plasmas**
- **What challenges and opportunities lie ahead for plasma technologies?**
  - **Materials Processing**
  - **Lighting**
  - **Atmospheric Pressure Plasmas**
  - **Bioscience**
  - **Nanoscience**
- **Concluding remarks**

# DEFINITION OF TECHNOLOGICAL PLASMAS

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- Technological plasmas are a power transfer media.
- Electrons transfer power from the "wall plug" to internal modes of atoms / molecules to make "benign" species into "reactive" species.

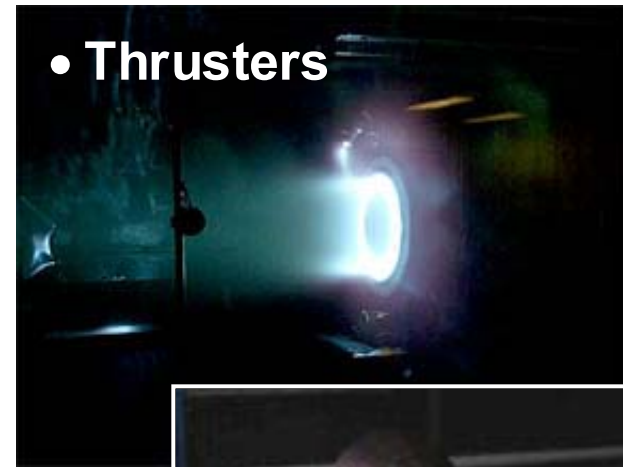


- Once activated, their physical or chemical potential may be used to make products (add or remove materials, photons...)

# COLLISIONAL LOW TEMPERATURE PLASMAS



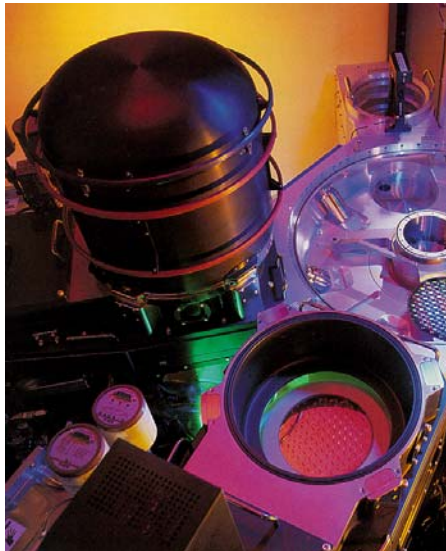
• Lighting



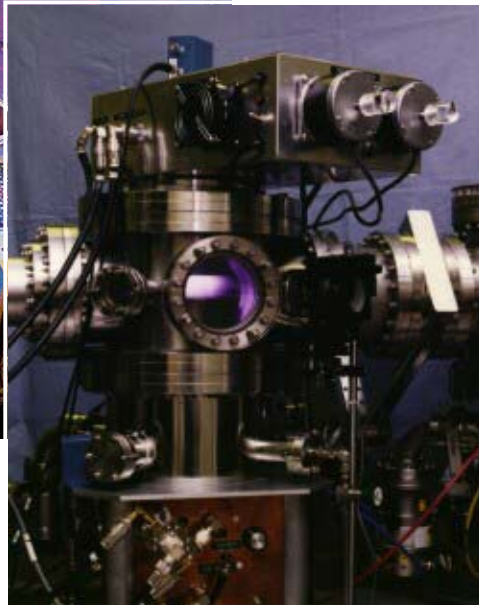
• Thrusters



• Spray Coatings



• Materials Processing



• Displays

# ***PLASMA MATERIALS PROCESSING FOR MICROELECTRONICS***

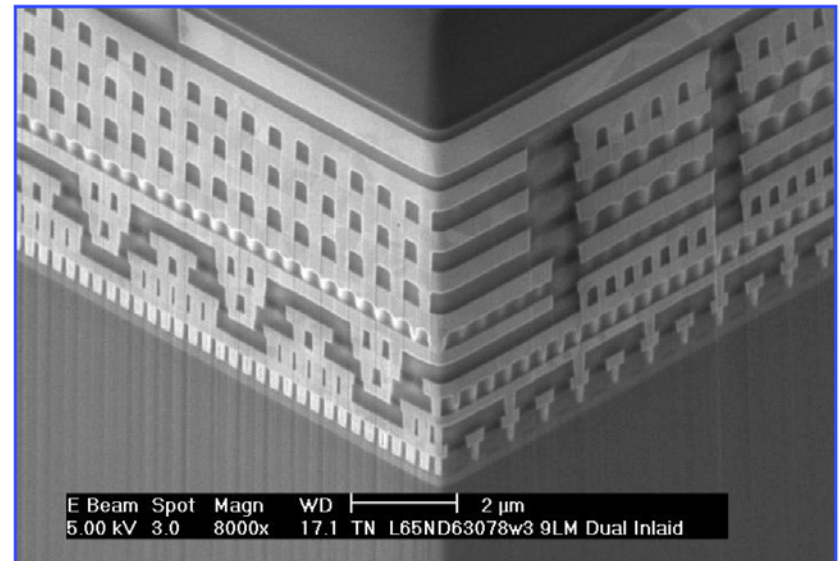
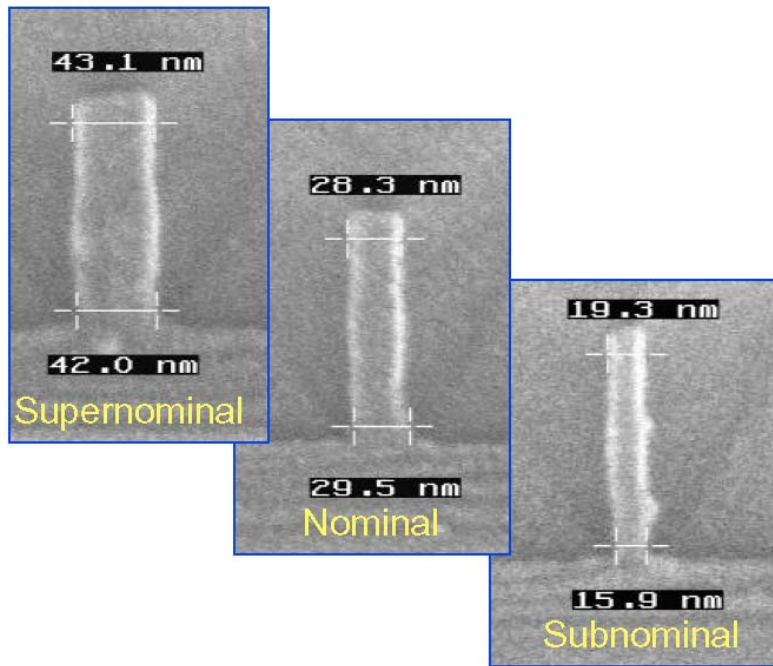
# PLASMA MATERIALS PROCESSING FOR MICROELECTRONICS

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- The fabrication of conventional microelectronics has met and bested extreme challenges as the nm scale is approached and exceeded.
- Plasma science has played a critical role in virtually all aspects of meeting these challenges
  - Physical Vapor Deposition
  - Plasma Enhanced Chemical Vapor Deposition
  - Etching
  - Cleaning
  - Passivation
  - Plasma sources of UV radiation for lithography (Hg lamps to EUV)

# PLASMA ETCHING-TRANSISTORS, INTERCONNECT

- Plasma etching is at the heart of microelectronics fabrication. Advance techniques have produced feature sizes below lithography limits.
- Challenges for etching novel low-k (dielectric) materials for interconnect have been met.



- Ref: F. Huang, P. Ventzek





# SOPHISTICATED PLASMA TOOLS

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- **AMAT Ionized Metal PVD**

- **Ref: Ashok Das**

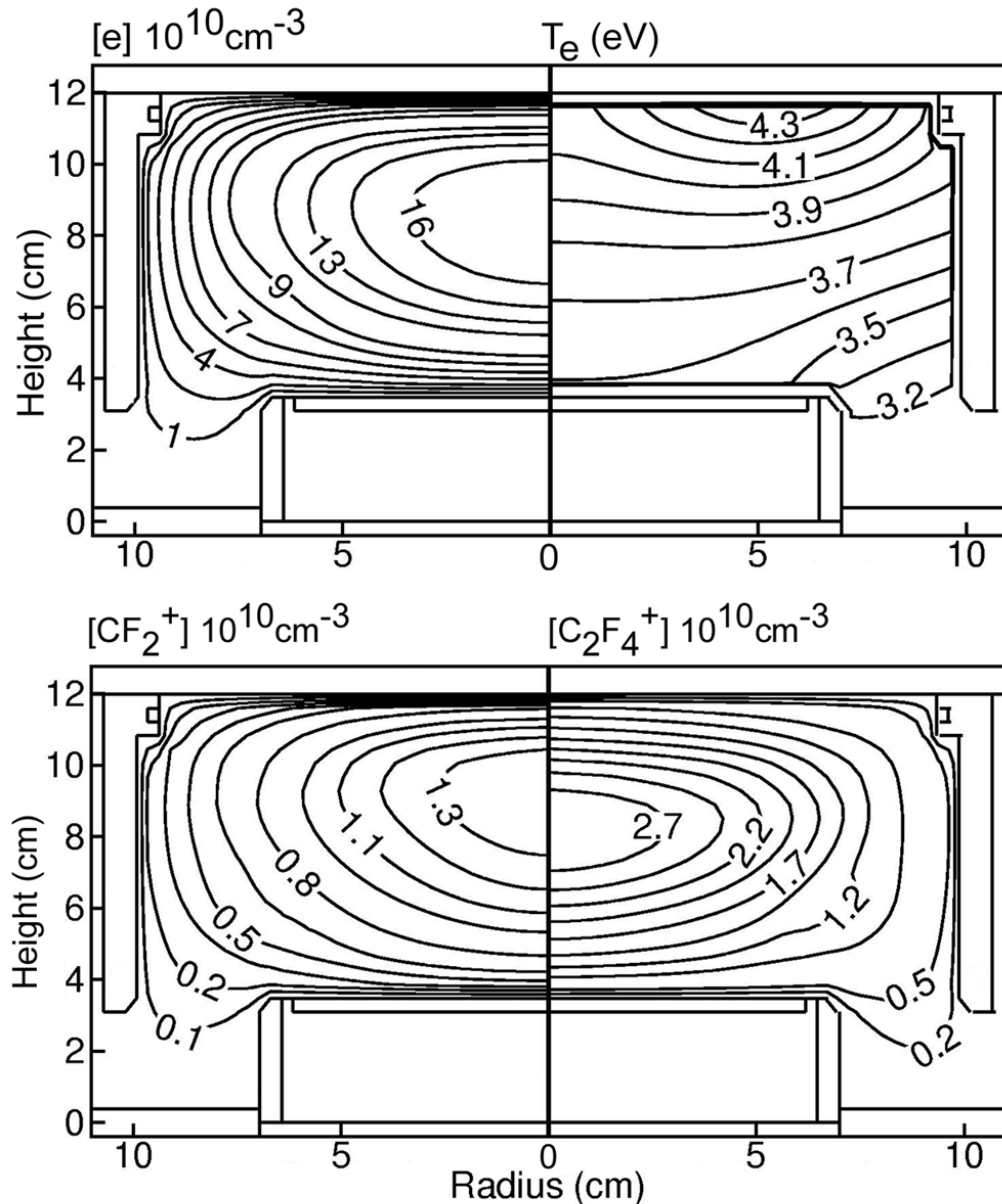


- **AMAT-Komatsu PECVD  
for flat panel displays**

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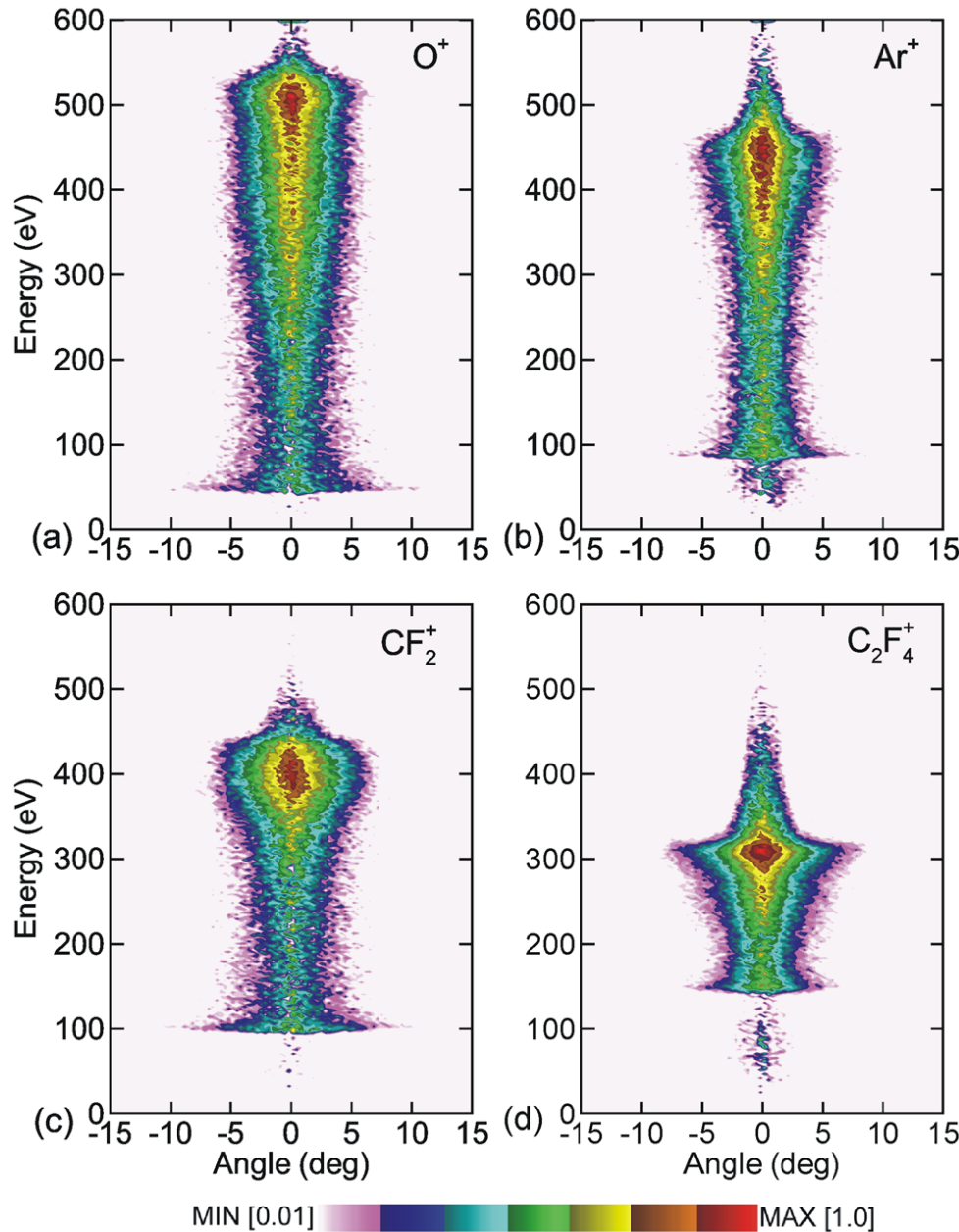
University of Illinois  
Optical and Discharge Physics

# PLASMA PROPERTIES: ICPs IN Ar/c-C<sub>4</sub>F<sub>8</sub>/CO/O<sub>2</sub>



- **Complex multi-component gas mixtures are used to optimize the flux of reactants to the substrate.**
- **Dozens of radicals and ions may be generated by dissociation and ionization of the feedstock gases.**
- **Ar/c-C<sub>4</sub>F<sub>8</sub>/CO/O<sub>2</sub> = 60/5/25/10, 10 mTorr, 600 W ICP, 13.56 MHz, 20 sccm.**

# IEADs TO SUBSTRATE: MERIES IN Ar/C<sub>4</sub>F<sub>8</sub>/O<sub>2</sub>



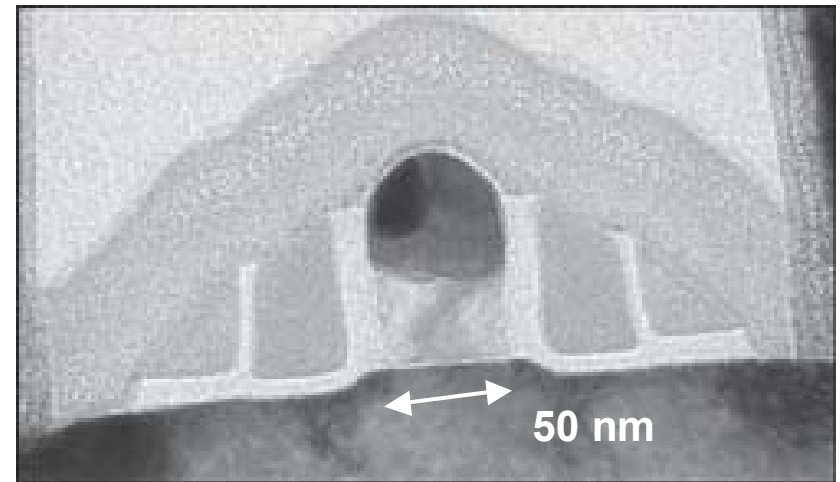
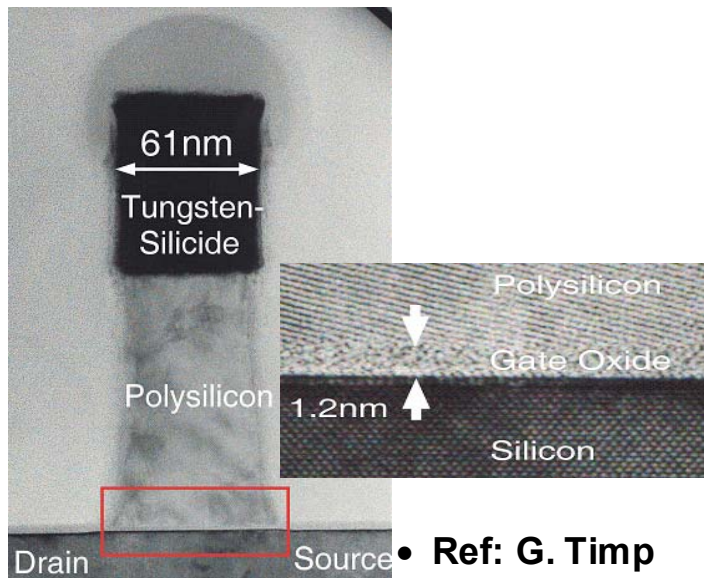
IEAD - 2000 W

- Acceleration of ions into the wafer by applied bias generates fluxes of a wide variety of ions.
- These Ion Energy and Angular Distributions (IEADs) activate etching processes.
- 40 mTorr, 2000 W MERIE, 215 sccm, Ar/C<sub>4</sub>F<sub>8</sub>/O<sub>2</sub> = 200/10/5, 100 G

# SELECTIVITY IN MICROELECTRONICS FABRICATION

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- Fabricating complex microelectronic structures made of different materials requires extreme *selectivity* in, for example, etching Si with respect to SiO<sub>2</sub>.

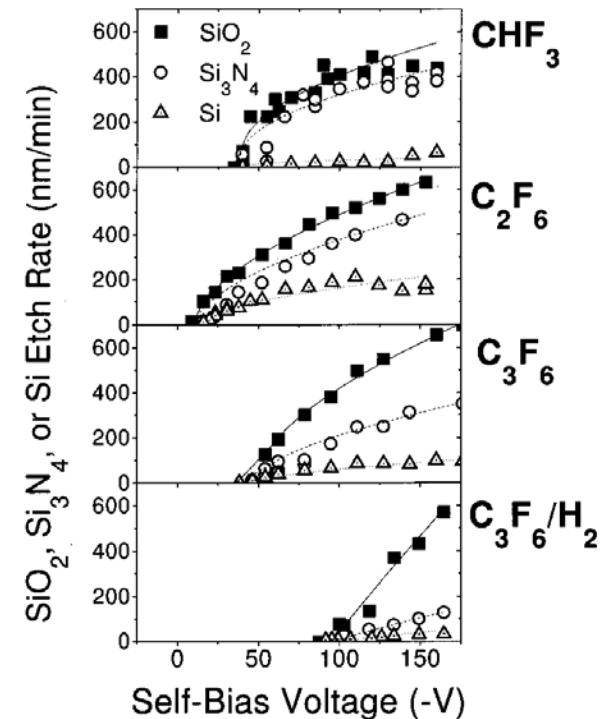
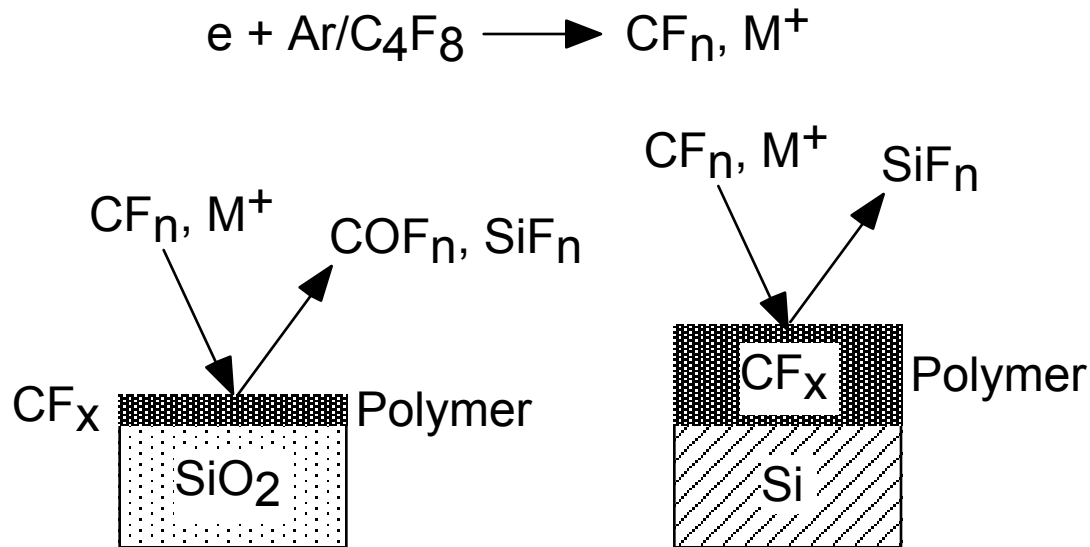


- AMD 90 nm Athlon 64

- Complex features are fabricated by selectively removing one material but not another with near monolayer resolution.

# FLUOROCARBON PLASMA ETCHING: SELECTIVITY

- Selectivity in fluorocarbon etching relies on polymer deposition from dissociation of feedstock gases.



- Compound dielectrics contain oxidants which consume the polymer, producing thinner polymer layers.
- Thicker polymer on non-dielectrics restrict delivery of ion energy (lower etching rates).

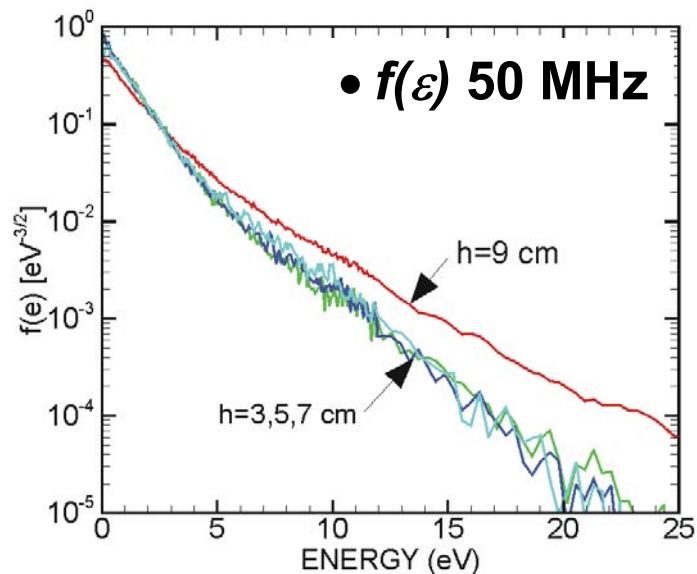
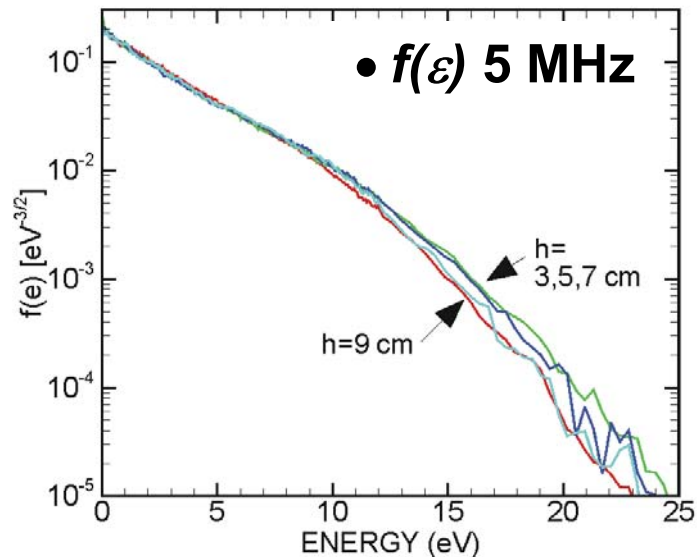
# CHALLENGES IN TAILORING PLASMAS FOR SELECTIVE ACTIVATION

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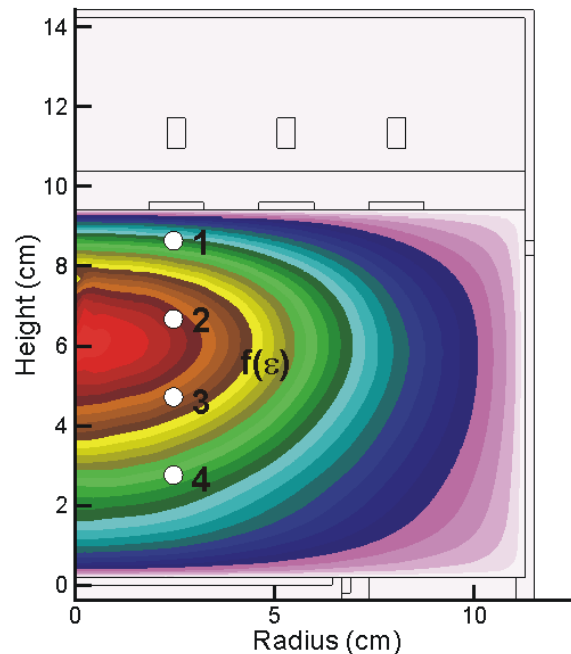
- **Advanced applications will require extreme selectivity by producing desired plasma chemical reactions and preventing undesirable.**
- **The ability to tailor the energy distributions of plasma particles is key to this selectivity.**
  - ***Tailored electron energy distributions:* Control formation of radicals and ions; best if also spatially segregated.**
  - ***Tailored ion energy distributions:* Should be narrow to differentiate thresholds.**
  - ***Tailored synergy between ions and neutrals:* Necessary for monolayer control of selectivity, deposition, end-point.**
- **Robust diagnostics to monitor, develop and control processes.**



# TAILORING $f(\varepsilon)$ BY FREQUENCY



- Plasma tools for multiple processes or recipes (different chemistries) require control of electron energy distribution for optimum generation of precursors.



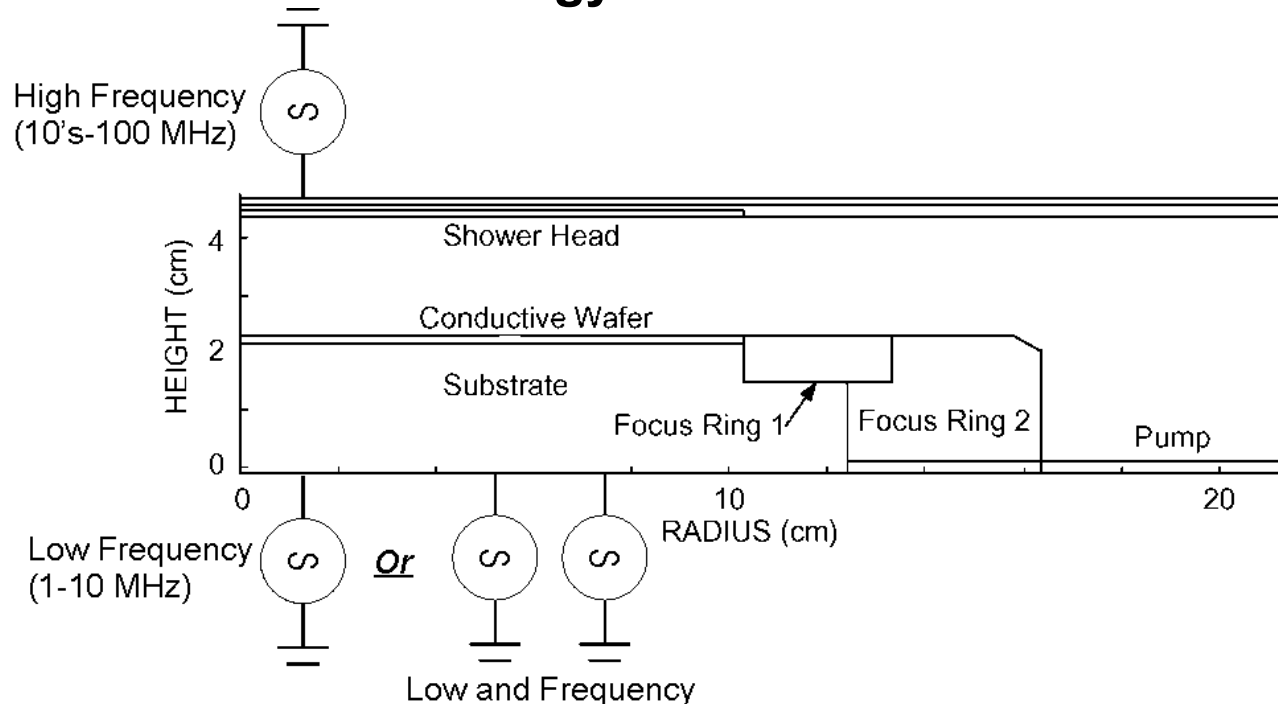
- [e], ICP, 10 mTorr, Ar/Cl<sub>2</sub> = 70/30.

Model results from HPEM  
Ref: K. Seaward, S. Samakawa

University of Illinois  
Optical and Discharge Physics

# TAILORING FLUXES USING MULTIPLE FREQUENCIES

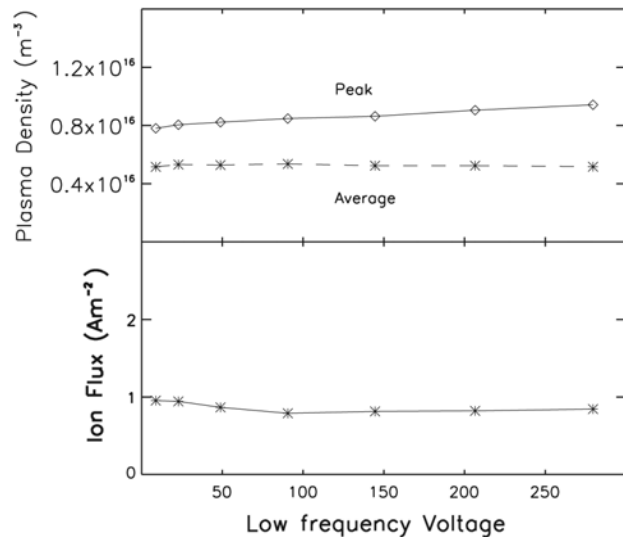
- **2 Frequency RIEs are rapidly becoming the tool of choice for dielectric etch.**
  - **High frequency is more efficient for heating electrons and so controls ionization and the magnitude of ion flux**
  - **Low frequency produces little electron heating but controls ion energy incident on the wafer.**



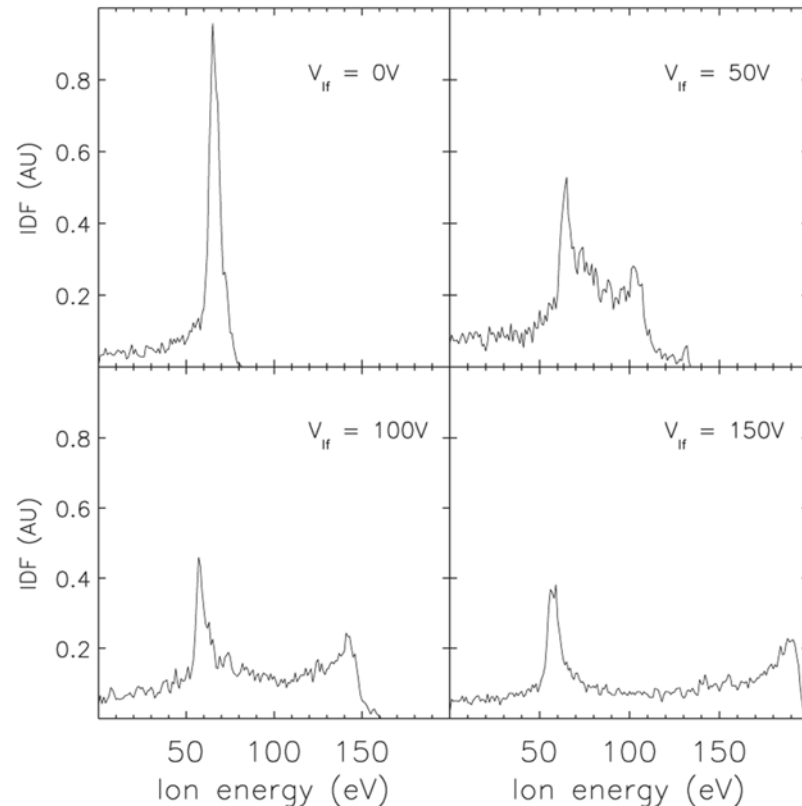


# TAILORING FLUXES USING MULTIPLE FREQUENCIES

- Over a wide parameter space, ion fluxes can be controlled by high frequency power; ion energy distribution controlled by low frequency.



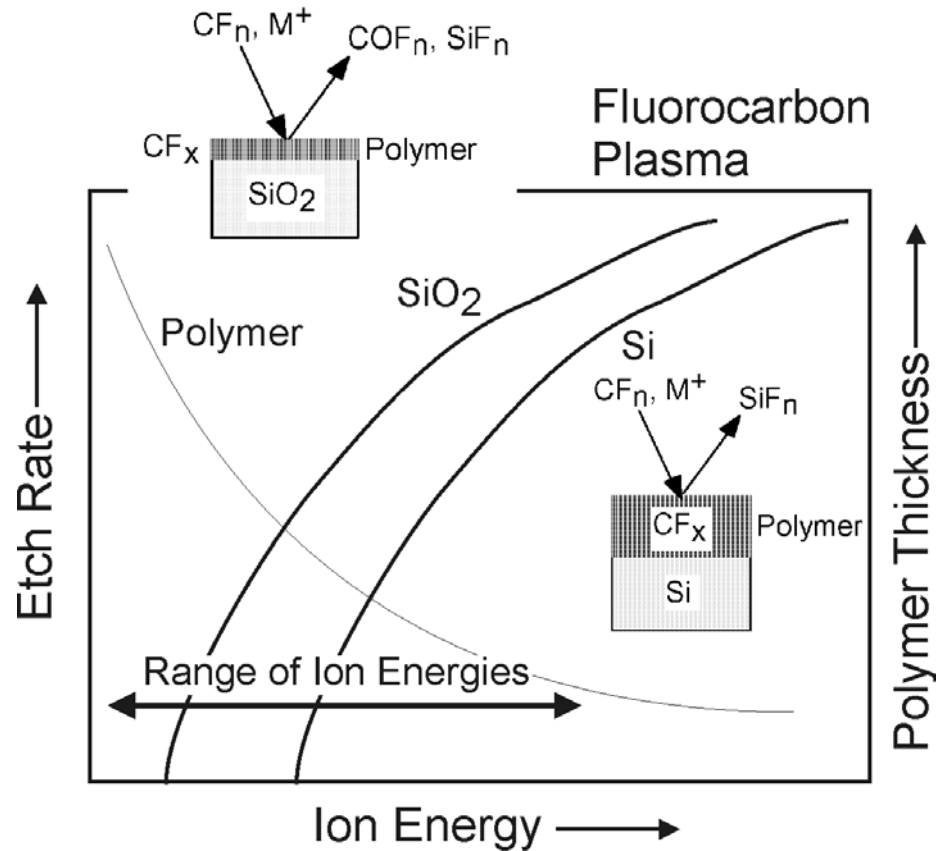
- Plasma density, Ion flux



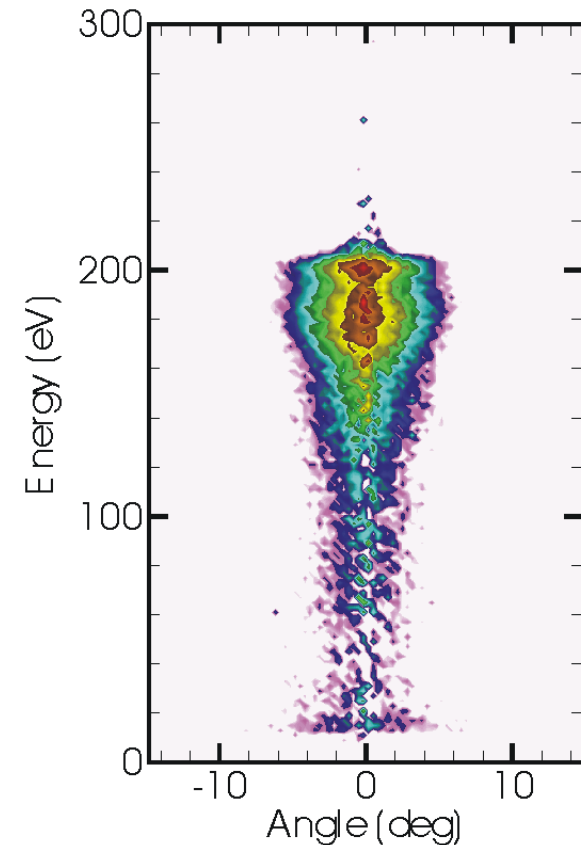
- Ion Energy Distributions

- Argon, 10 m Torr
- Boyle, Ellingboe, Turner, PSST 13, 493 (2004)

# DIFFICULT TO ACHIEVE SELECTIVITY: BROAD IEADS



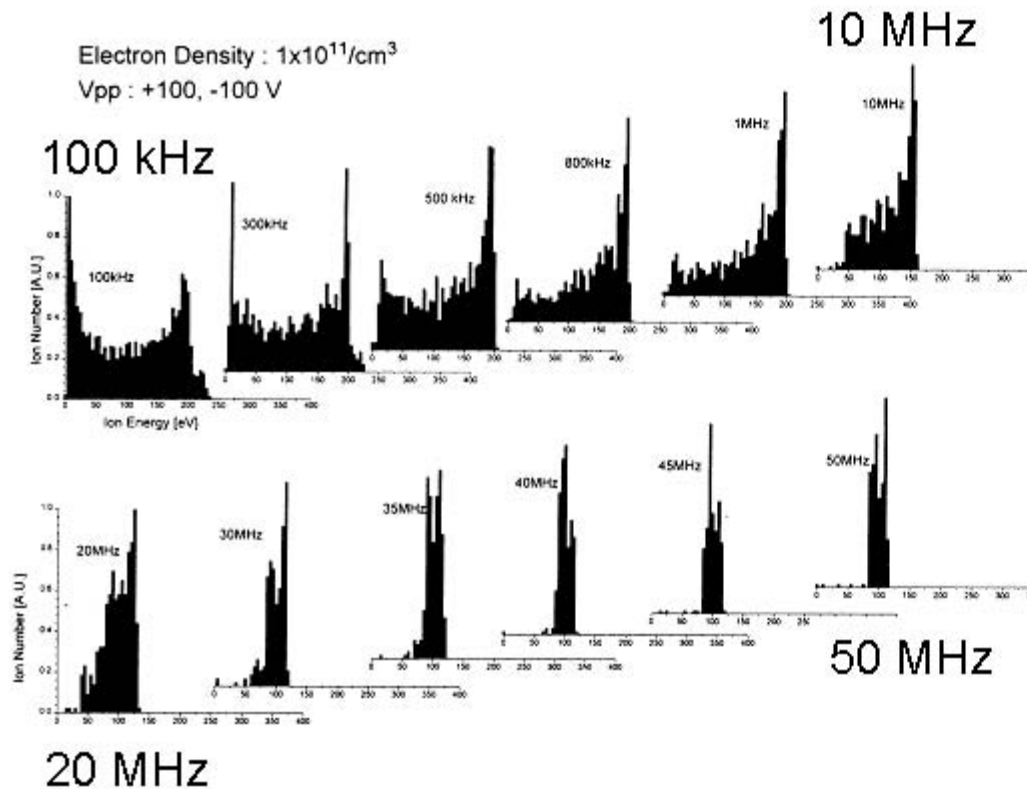
- **Broad ion energy distributions makes it difficult to resolve thresholds for etching; and so selectivity is poor.**



- **Ar, 40 mTorr, 300 sccm, 500 W 40 MHz (top), 500 W 5 MHz (bottom), 100 G**

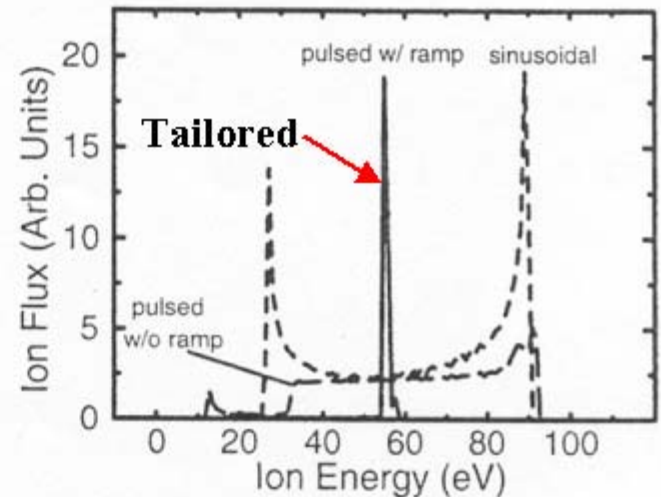
University of Illinois  
Optical and Discharge Physics

# *Ion Energy Control – Tailored Waveform through Frequency and Active Electronics*



• From from Hyun-Ho Doh, et al, JVST A 15 664 (1997).

**Tailored bias waveform:  
 Single peak, FWHM 2 eV**



• From S.-B. Wang and A.E. Wendt, JAP 88 643 (2000)

**Ref: K. Seaward**

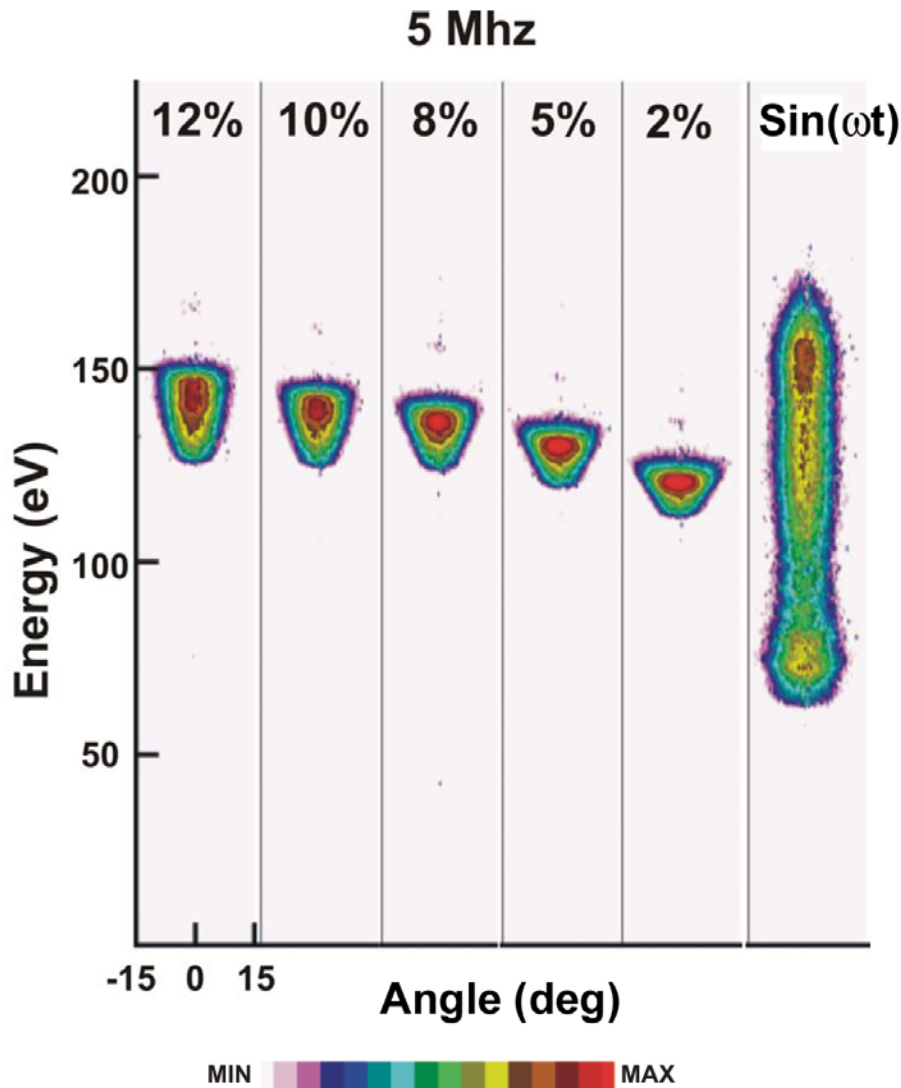


**Agilent Technologies**

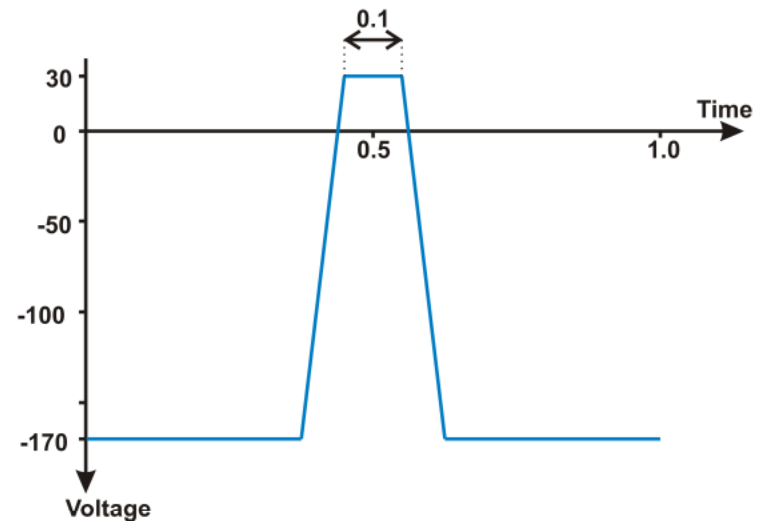


Electronic Research Laboratory  
 Plasma Processes Project  
 K. L. Seaward, 9/15/03

# NARROW IEDS: CUSTOMIZED BIAS WAVEFORM

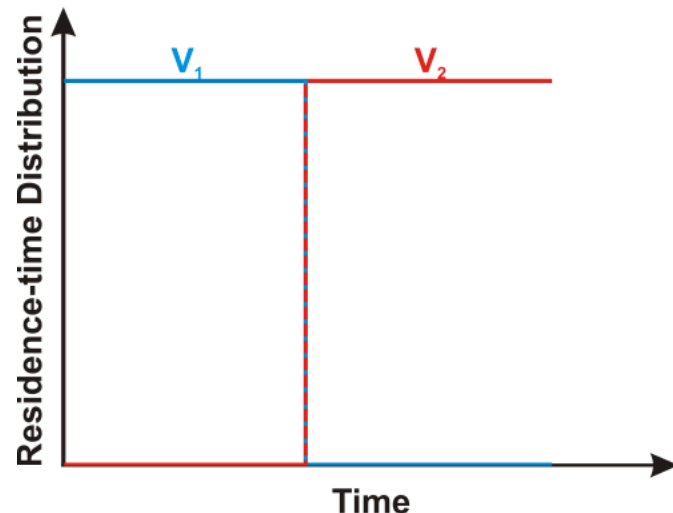
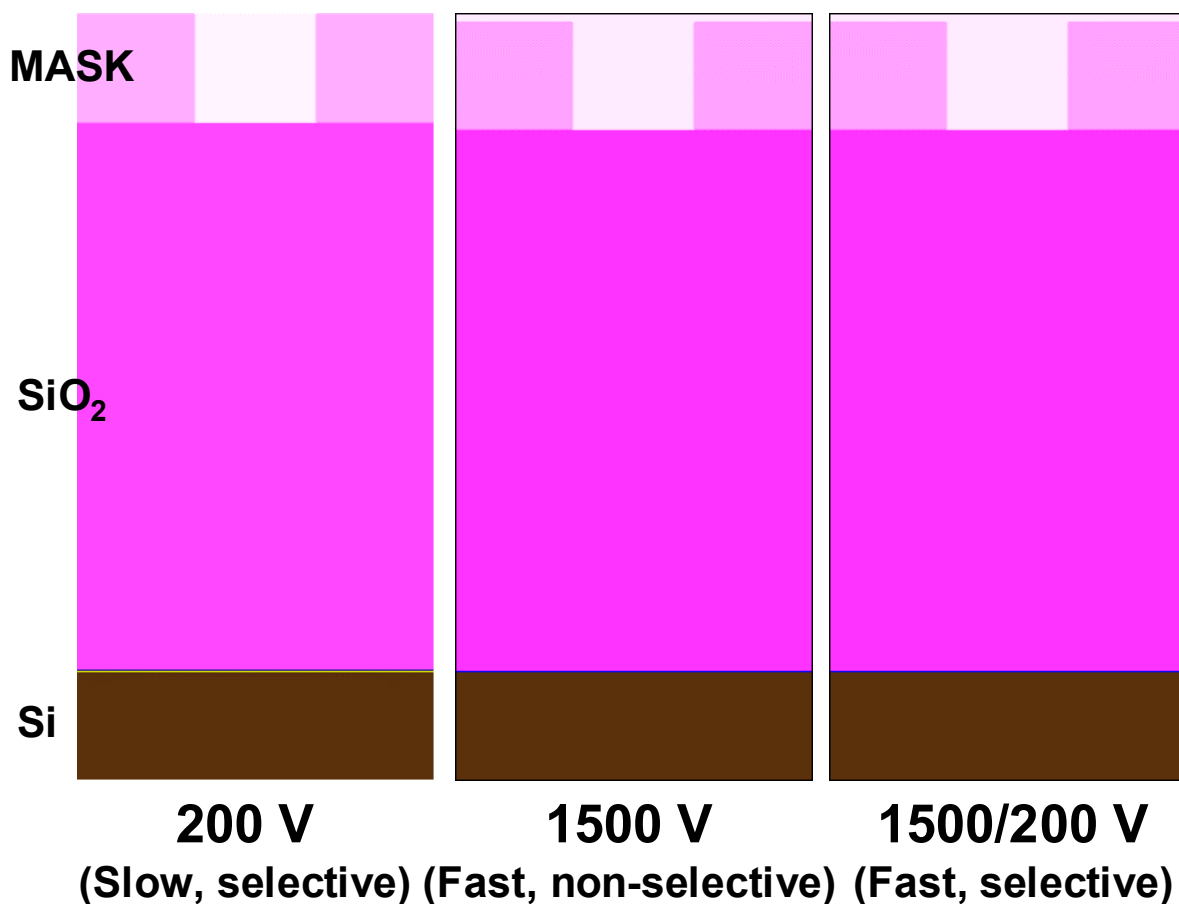


- Non-sinusoidal biases enable control of sheath potential, and narrowing of the IED.



- 15 mTorr, 500 W, 200 V<sub>p-p</sub>,  
Ar/C<sub>4</sub>F<sub>8</sub> = 75/25, 100 sccm

# SPEED AND SELECTIVITY: CUSTOM WAVEFORMS



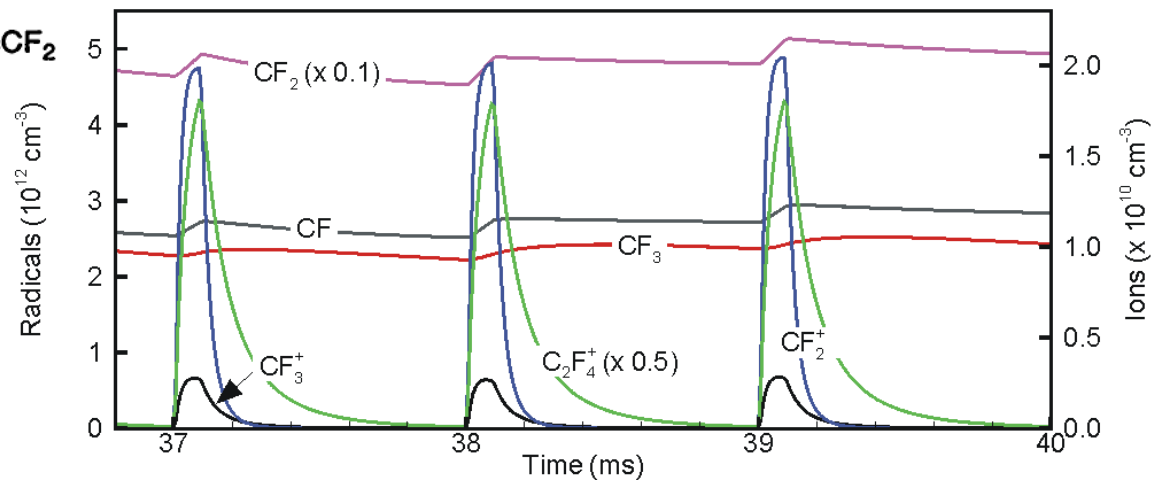
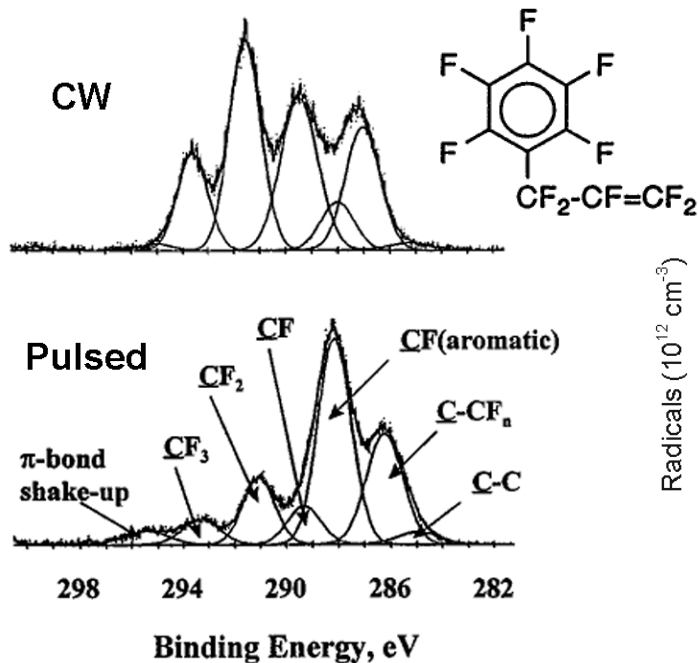
- 15 mTorr, Ar/C<sub>4</sub>F<sub>8</sub> = 75/25, 100 sccm, 10 MHz/10%

- Recipes combining custom waveforms and dynamically adjusted biases optimize speed and selectivity.

ANIMATION SLIDE  
CLICK ON FIGURES-AVI FILES IN SAME DIRECTORY  
See icpp\_animate.ppt

# TAILORING FLUXES THROUGH PULSING

- Processing of thin films depends on the synergy between energetic ions and radical fluxes. Pulsed plasmas which control these contributions produce unique films not otherwise attainable.



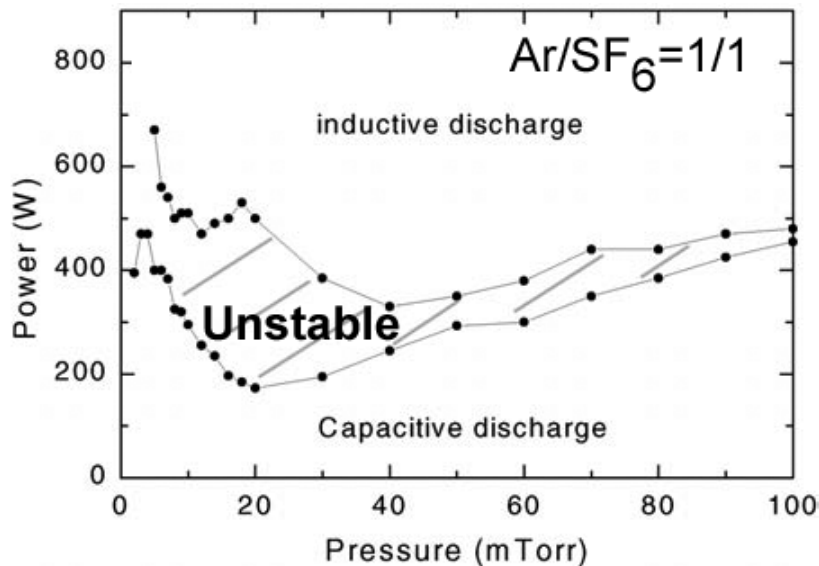
- Deposition of low-k fluorocarbon film from perfluoroallyl benzene [L. Han, JVSTB 18, 799 (2000)]

- Pulsed ICP Ar/ $C_4F_8=70/30$ , 15 mTorr

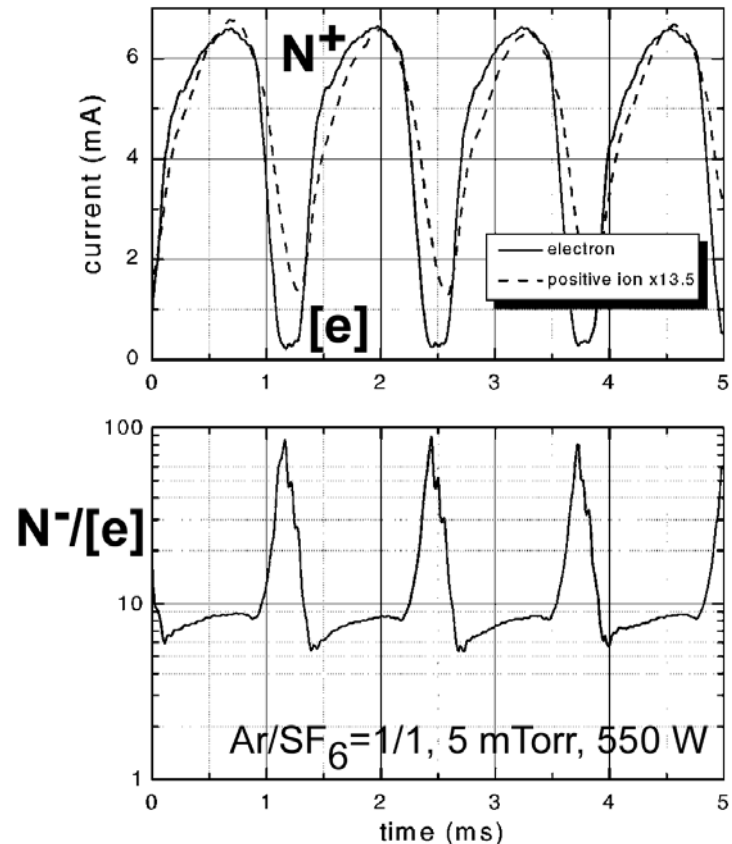
- Model results from GLOBAL\_KIN  
Ref: K. Seaward

# INSTABILITIES: ELECTRONEGATIVE PLASMAS

- Although rf (10's MHz) excited plasmas operate in a quasi-dc basis, instabilities regularly occur. Most plasma processing tools likely have instabilities which make reproducibility difficult.



- Ionization instability in inductively coupled Ar/SF<sub>6</sub> plasma for etching.
- Chabert, Lichtenberg, Lieberman, Marakhtanov PSST 10, 478 (2001)



# **PLASMA DIAGNOSTICS HAVE PLAYED A CRITICAL ROLE AND ARE MOVING CLOSER TO THE PRODUCT**

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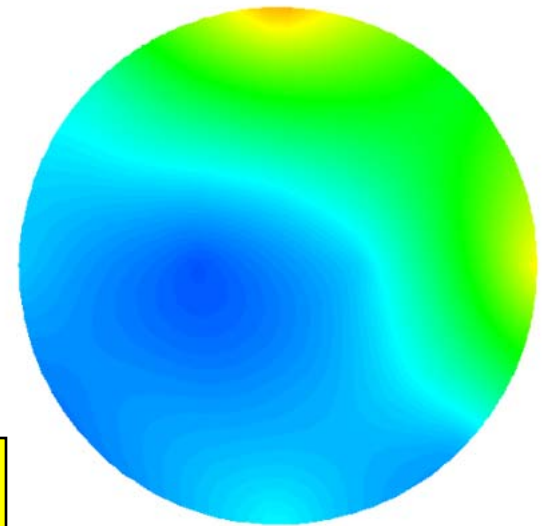
- **Plasma process and equipment design have and will continue to critically rely on advanced plasma diagnostics.**
- **Real time control strategies, a requirement for sub-90 nm processing, must also rely on robust, cost-effective diagnostics.**
- **The most mature plasma diagnostics are typically too far removed from critical measurements of activation of surface processes.**
- **Non-intrusive diagnostics which provide the state of activating species impinging on surfaces are required for a complete picture.**



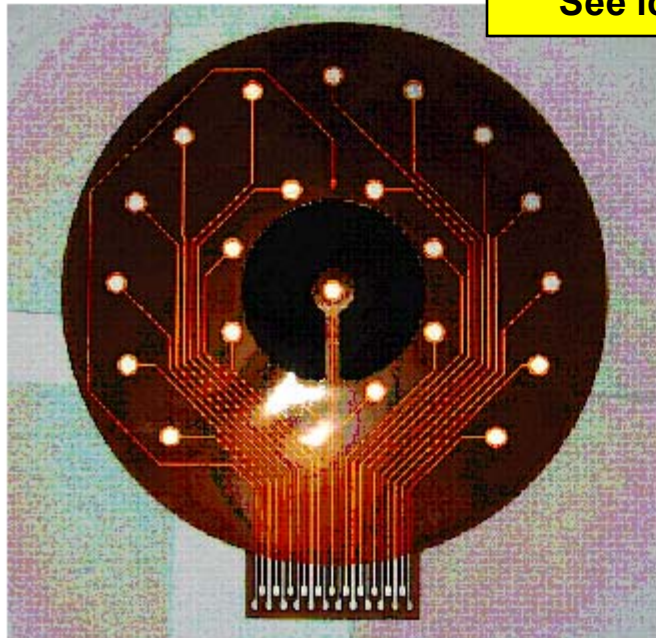
# On-Wafer Ion Flux Probe Array

- An on-wafer probe array providing  $J_+(r, \theta)$  is used to investigate factors that affect the plasma stability and etching uniformity using plasma etching chemistries.

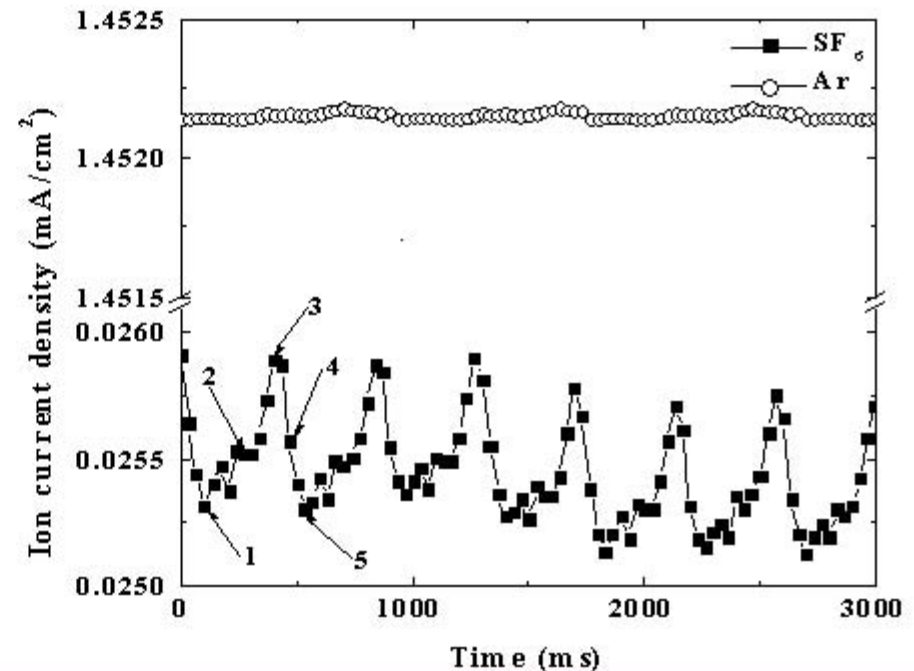
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See icpp\_animate.ppt



80 mTorr SF<sub>6</sub>, 200 W

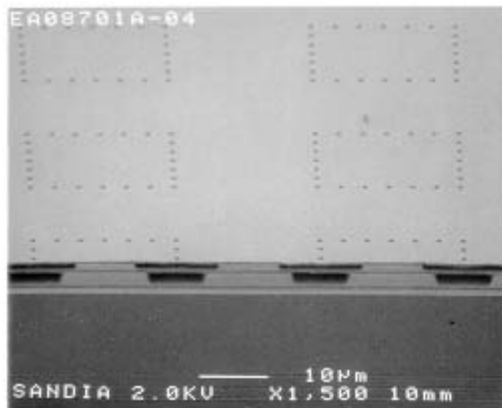
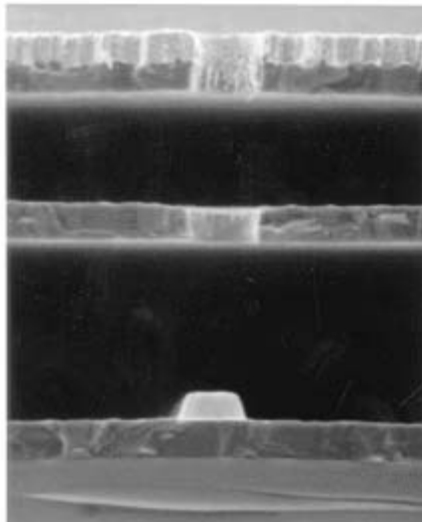


Ref: E. Aydil

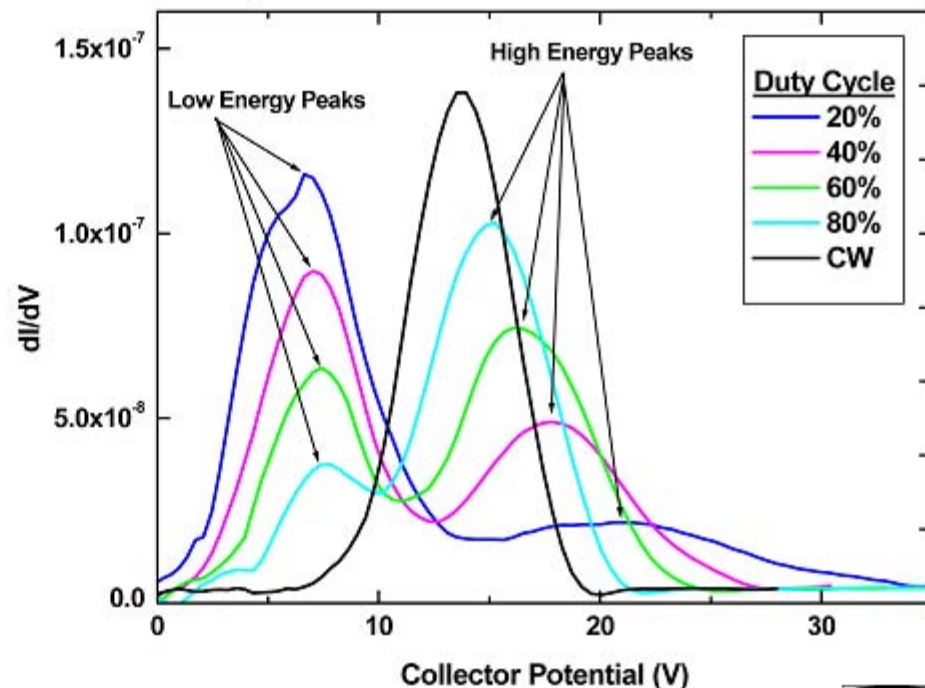


# Sub-micron Retarding Field Energy Analyzer on a Si Substrate

- MEMS fabricated analyzers (0.7~0.8  $\mu\text{m}$  grid holes on 3.75  $\mu\text{m}$  centers) provide inobstrusive measurements of ion energy distributions directly on surfaces of interest.



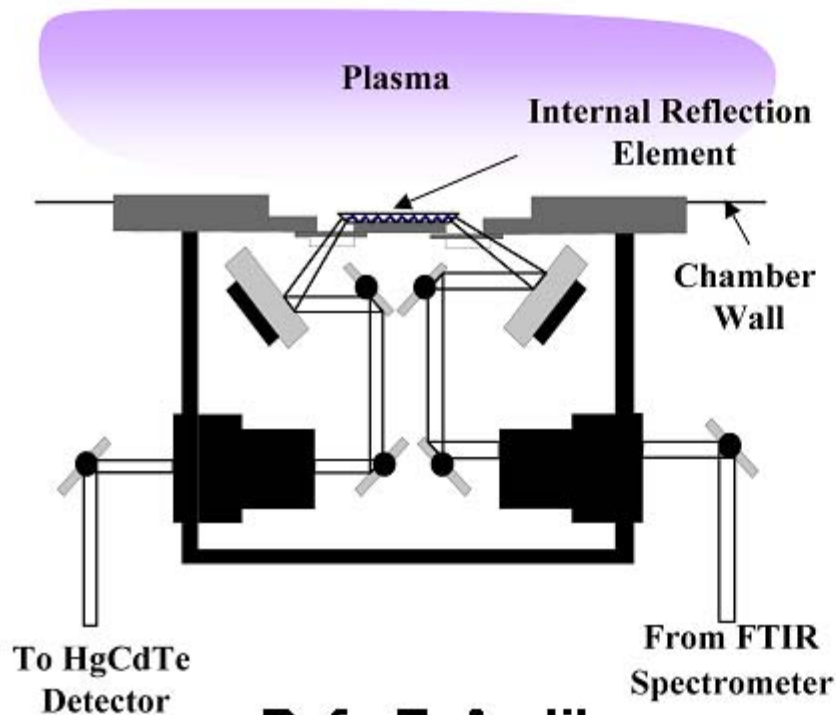
Measured Ion Energy Distributions  
100 W<sub>ip</sub>, 40 usec pulse period, 5 mTorr, 100 sccm Ar



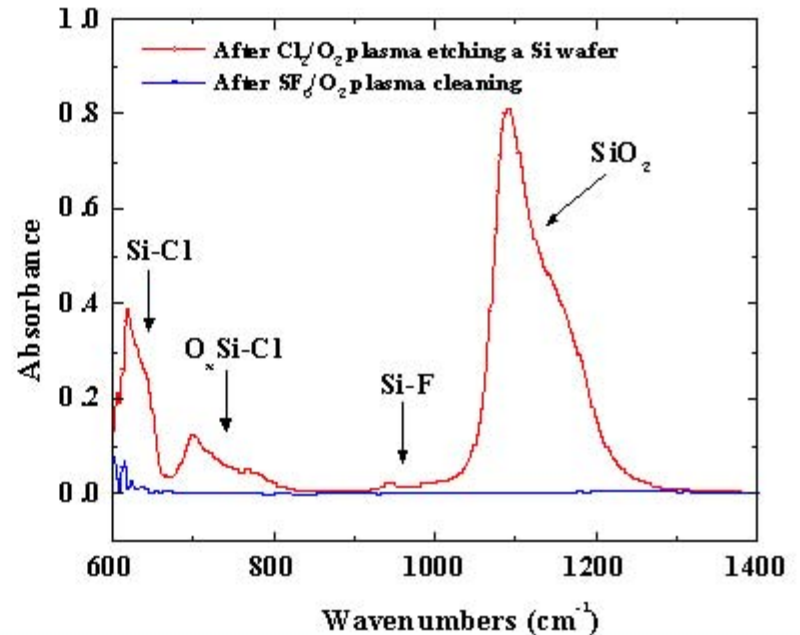
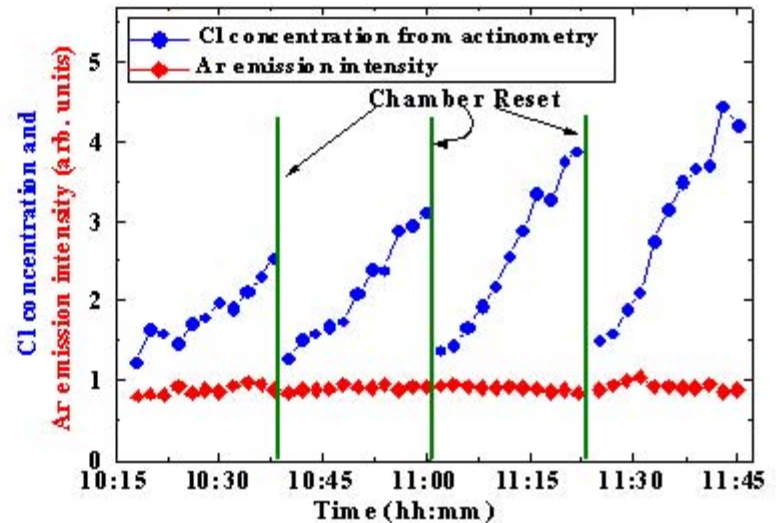
Ref: M. Blain

# MTIR-FTIR Wall Probe

- Drift in Cl results from change in the Cl recombination on the walls due to deposition of Si-O-Cl products.
- Exposure to SF<sub>6</sub>/O<sub>2</sub> plasma resets the walls to a reproducible condition.



Ref: E. Aydil



Cl<sub>2</sub> 10 mTorr, 800 W, 100 sccm

# MATERIALS PROCESSING: CHALLENGES

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- **New materials (metal gates, low-k dielectrics, high-k dielectrics, SiGe/SOI substrates, porous materials).**
- **Increasing demands on etch selectivity.**
- **Shorter development cycle (6 months...)**
- **Lower thermal budgets (lower temperature processes)**
- **More controllable knobs to provide reliable real time control.**
- **Use of plasmas as processing tools (e.g., self assembly) as opposed to pattern replication.**
- **Reduced cost of ownership through plasma tools which are used for multiple processes.**
- **Improved and more relevant contributions from modeling.**
  
- **Ref: J. Cook, T. Mantei, P. Schenborn, P. Ventzek, D. Manos**

# ***PLASMAS FOR LIGHTING***

# **IMPACT OF PLASMA LIGHTING TECHNOLOGIES**

- **Annual US energy use for lighting is 750 TWH (8.2 quads)**
  - **8.3 % of total energy consumption**
  - **22% of total electrical energy consumption.**
- **Plasmas are 59% of lighting energy use (13% of total). There are 2.6 billion plasma lighting sources in the US.**
- **Replacing incandescent lamps with plasma sources will decrease US electrical energy use 5% [20 nuclear power plants or 1.2 Million barrels of oil/day (10% of imports)].**
- **Greenhouse gas emission commensurately reduced.**
- **Improving efficiencies and use of plasma lighting will enormously impact the worldwide economy and improve the environment.**
  
- **Ref: U.S. Lighting Market Characterization, Navigant Consulting, 2002**
- **DOE Annual Energy Outlook 2003**



# HID lamps for illumination and Projection

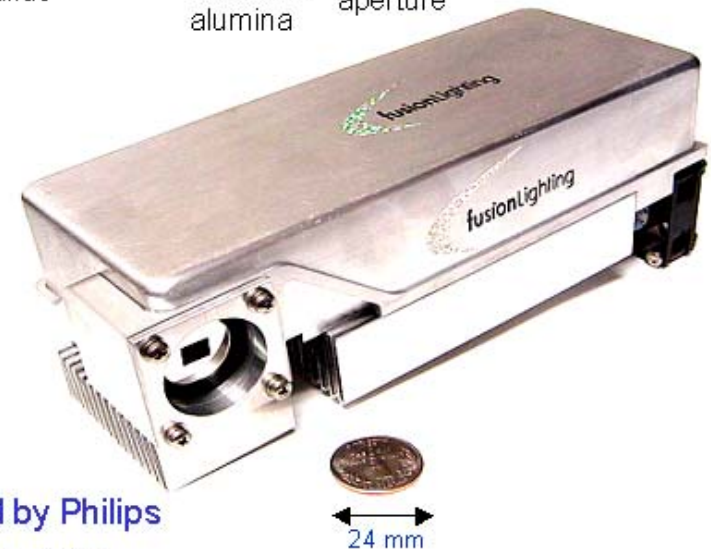
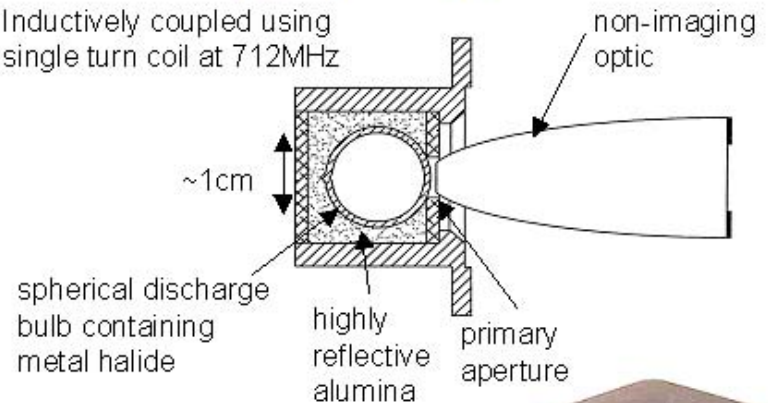
## CMH white-light metal halide

- precision arc tube made from alumina
- Na, Tl and rare earth iodides + Hg
- high efficacy and good colour result from high vapour pressures
- designed to be operated from electronic control gear



## Fusion Lighting LCD projector unit

Inductively coupled using single turn coil at 712MHz



## HID projection lamps pioneered by Philips

Short arc mercury (~200 bar) arc tube – light produced by atomic lines and molecular bands.



# Quartz lamps

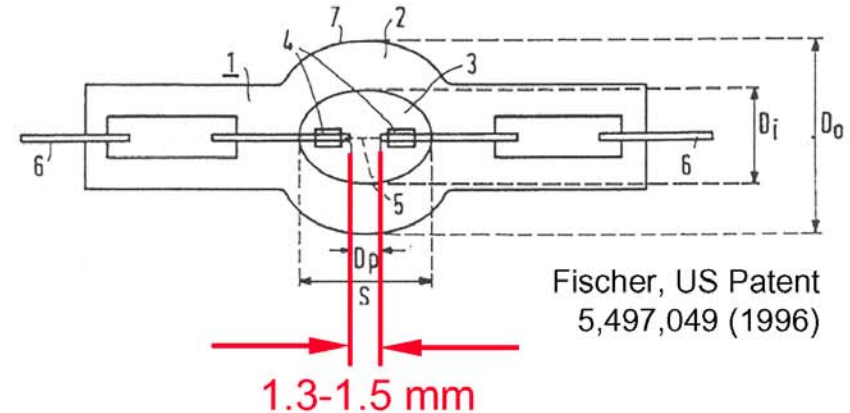
State of the art

- **Ultra-high-pressure mercury**

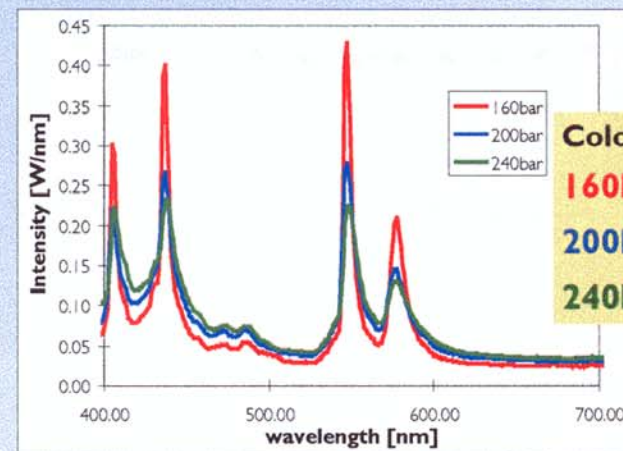
- quartz arc tube
- mercury + bromine dose
- 200–240 bar operating pressure
- 1.3–1.5 mm arc gap
- 8500 K color temperature
- excellent lumen maintenance
- minimal color separation and color shift over life
- 1000–2000 hour life
- 100–150 watts (6000–10000 lumens)

- **Limitations and shortcomings**

- spectrum is deficient in red
  - *color efficiency ~70 percent*
- cannot scale up wattage
  - *without shortening life*
- cannot scale down arc gap
  - *without reducing efficacy*



## High Mercury Pressure for High Color Efficiency



**Color Efficiency:**  
**160bar: 53%**  
**200bar: 66%**  
**240bar: 73%**

Mönch, Fischer, and Derra

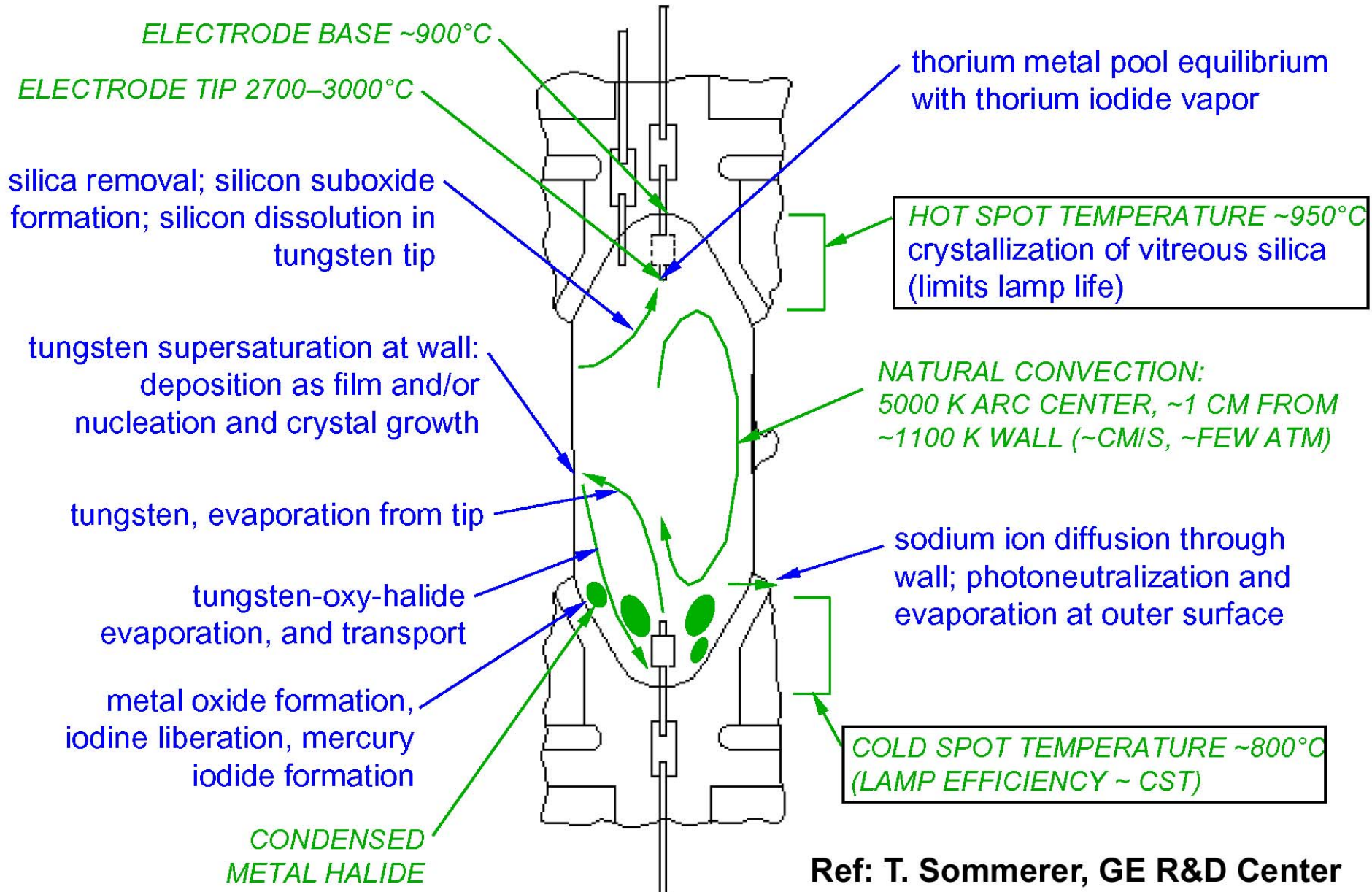
Ref: T. Sommerer, GE R&D Center





# Material transport processes

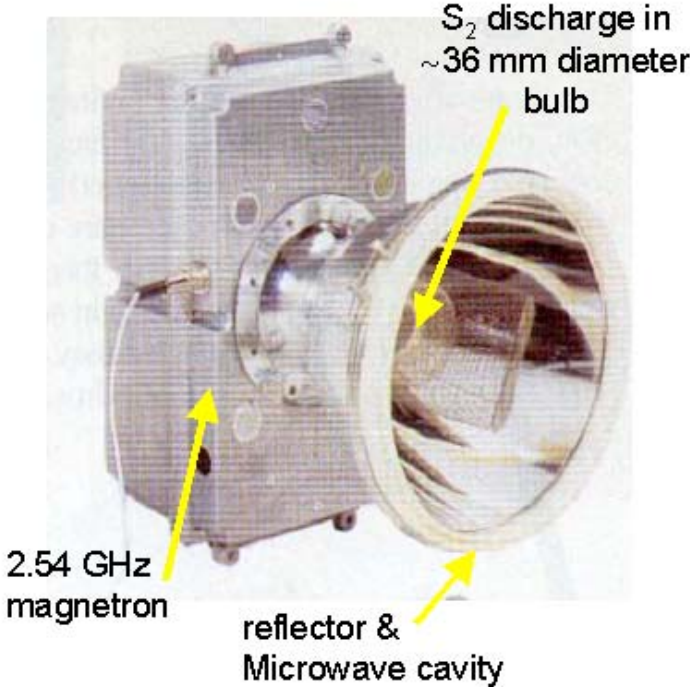
## Quartz metal halide lamp



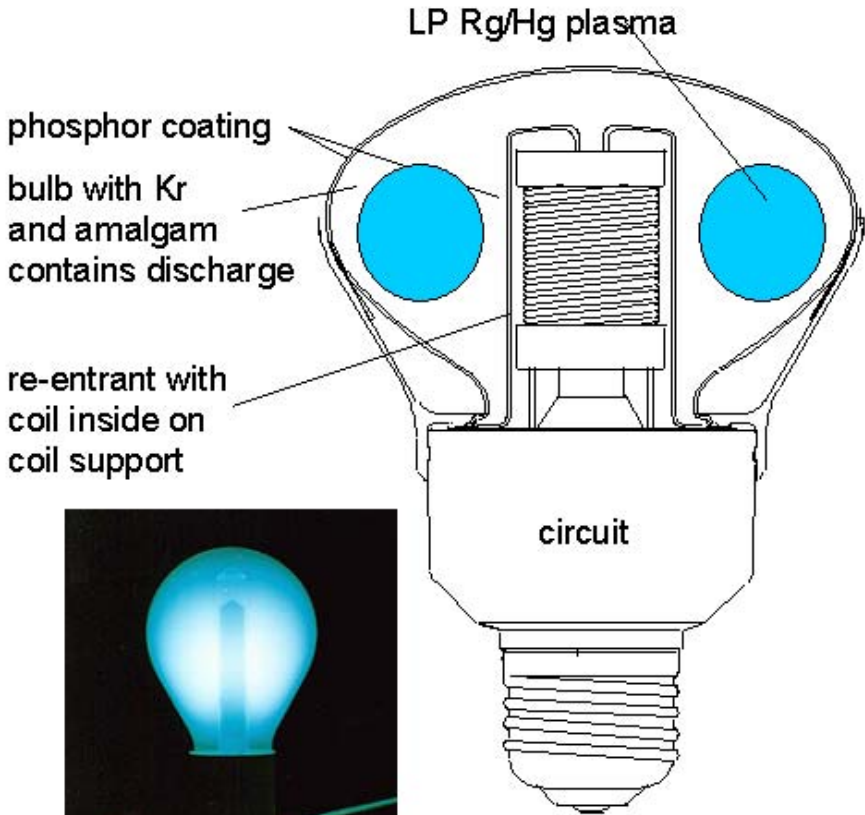
Ref: T. Sommerer, GE R&D Center

# Electrodeless – $\mu$ wave and RF sources

- Sulphur discharge – Fusion Lighting record 170 lumen/microwave W



- Inductively coupled Rg/Hg lamps



*System design*

**Ref: David Wharmby**

# LIGHTING: ACCOMPLISHMENTS AND CHALLENGES

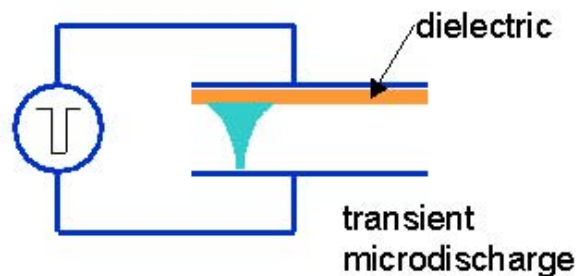
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- **Efficient white sources based on Hg plasmas in fluorescent and arc lamps; and non-white metal vapor lamps.**
- **Challenges:**
  - **Highly efficient non-Hg (or Cd, Pb,...) plasma white-light sources or near UV which match phosphors (rare gases, excimers, metal halides, molecular radiators)**
  - **Thermodynamics of high pressure plasmas.**
  - **Improving understanding of plasma-surface interactions to extend lifetimes (cathodes); and glow-to-arc transition.**
  - **Quantum splitting phosphors to improve utilization of UV (2 visible photons from 1 UV reduces US energy use 5-10%).**
  - **Leverage lighting technologies to other application (e.g., UV sources for water treatment, and vice-versa.**
  - **Radiation driven non-LTE effects in high pressure lamps.**

## Dielectric barrier discharge (DBD)

- Osram Planon lamp
- Xe discharge with UV radiation from  $\text{Xe}_2^*$  excimer
- 60% efficiency to UV – then converted to visible with phosphor

Schematic diagram



- Osram innovations in electrode structure and pulse power format for uniformity.





# MODELING ADVANCES ADDRESS TECHNOLOGY DEVELOPMENT

- The pressure of (hot) HIDs is many atm.
- After turn off, the tube must cool to reduce the metal density (increase E/N) so that the available voltage can re-ignite the lamp.
- Lamp designs are often driven by startup considerations.
- Electron density



100/ 0.001    99.9/0.1    97/3    7/3  
Ambient    50 C    140 C    220C

Ar (75 Torr cold fill) / Hg



$5 \times 10^8 - 5 \times 10^{11} \text{ cm}^{-3}$   
0-450 ns

ANIMATION SLIDE  
CLICK FIGURES-AVI FILES IN SAME DIRECTORY  
See icpp\_animate.ppt

University of Illinois  
Optical and Discharge Physics



GE R400

# ***ATMOSPHERIC PRESSURE PLASMAS***

# ATMOSPHERIC PRESSURE PLASMAS

---

- **Atmospheric Pressure Plasmas (APP) have had tremendous technological impact**
  - **High power lasers (e.g., Excimer lasers)**
  - **Lighting Sources (e.g., HID lamps)**
  - **Ozone generators**
  - **Modification of surfaces**
  - **Toxic gas abatement**



- **Atmospheric pressure DBD ozone generator**

**Ref: U. Kogelshatz**

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**University of Illinois  
Optical and Discharge Physics**

# OPPORTUNITIES: ATMOSPHERIC PRESSURE PLASMAS

## THE CHALLENGE

---

- APP's provide the potential to selectively generate activated species (radicals, ions and photons) for modification and cleaning of surfaces at low cost.
- Most (many) industrial processes performed with liquid solvents could in principle be performed with APP generated radicals.
- The environmental impact of eliminating liquid solvents for cleaning of parts, removal of paint, functionalizing or sterilizing surfaces would be immense.
- Advanced concepts include improvement of combustion processes, chemical and biological remediation, sterilization, microplasma devices, control of aeronautical flows.
- The potential for APPs to perform “high value” manufacturing is literally untapped.

Ref: B. Ganguly

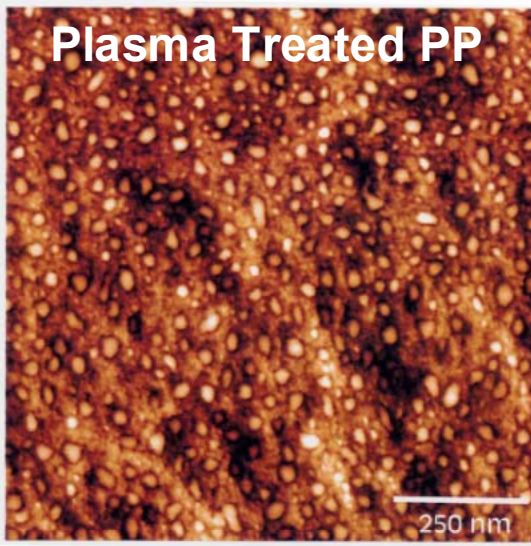
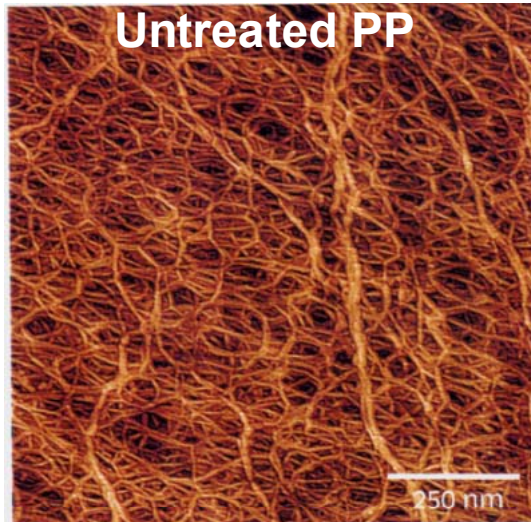
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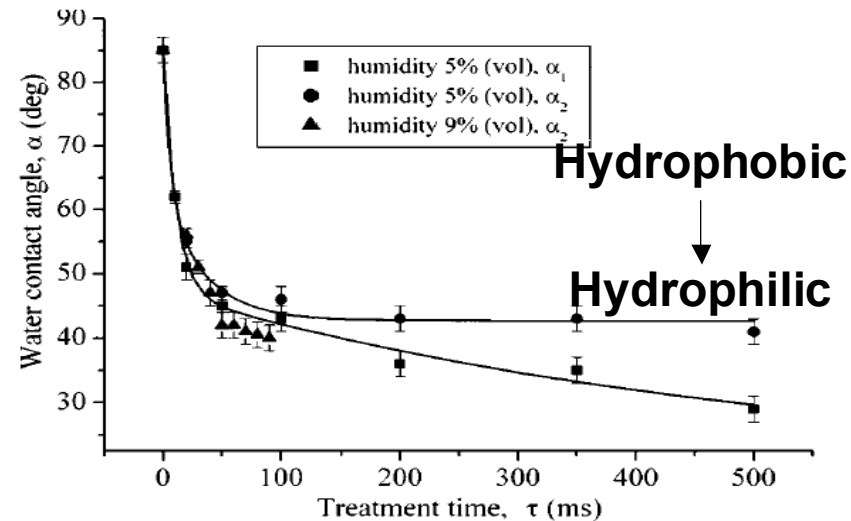
***ATMOSPHERIC PRESSURE PLASMAS  
FOR MATERIAL AND SURFACE PROCESSING:  
COMMODITY TO HIGH VALUE***

# PLASMA SURFACE MODIFICATION OF POLYMERS



• M. Strobel, 3M

- To improve wetting and adhesion of polymers atmospheric plasmas are used to generate gas-phase radicals to functionalize their surfaces.



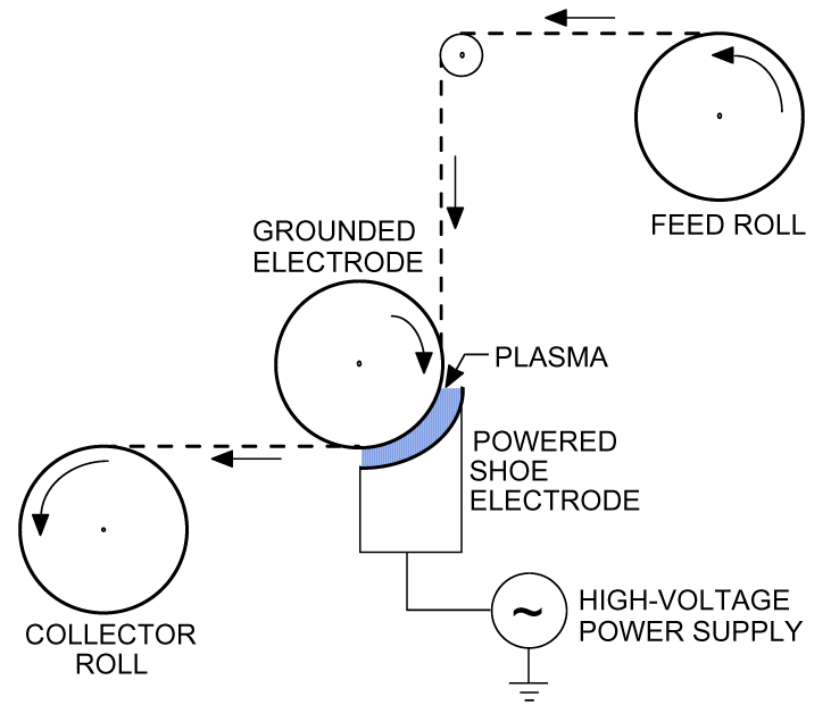
- Polyethylene, Humid-air
- Akishev, Plasmas Polym. 7, 261 (2002).

# POLYMER TREATMENT PLASMA TOOL

- Web based corona plasmas treated sheet polymers for improved surface functionality.



Tantec Inc.



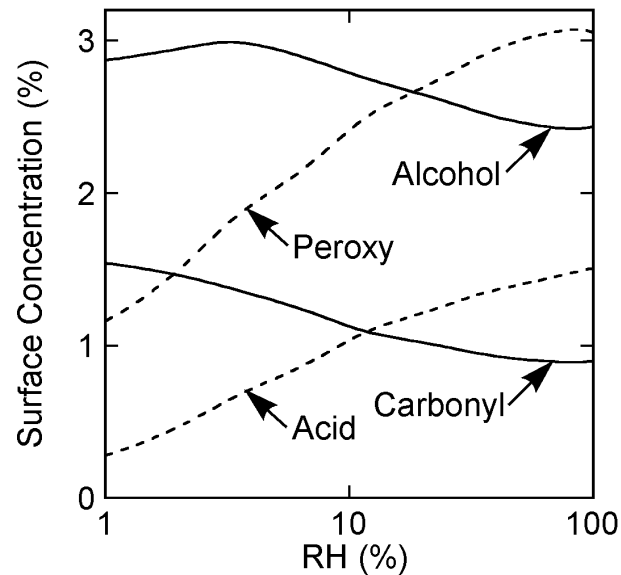
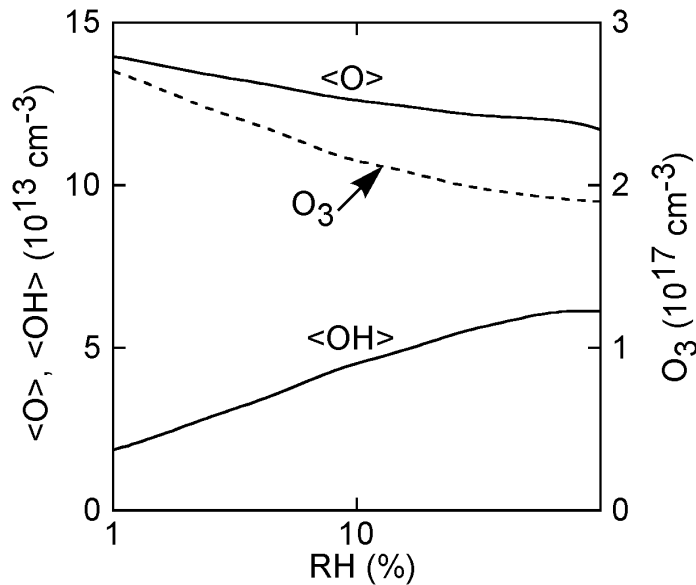
- TYPICAL PROCESS CONDITIONS:  
Web speed : 10 - 200 m/min  
Residence time : a few s  
Energy deposition : 0.1 - 1.0 J cm<sup>-2</sup>  
Applied voltage : 10-20 kV at a few 10s kHz  
Gas gap : a few mm

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# FUNCTIONALIZATION OF POLYPROPYLENE

- Control of surface energy by plasma treatment results from functionalization with hydrophilic groups.
  - Carbonyl (-C=O)
  - Alcohols (C-OH)
  - Peroxy (-C-O-O)
  - Acids ((OH)C=O)
- Functionalization depends on radical fluxes and process parameters [gas mix, energy deposition, relative humidity (RH)].



• Air, corona plasma, 300 K, 1 atm

# THE ROLE OF PLASMAS IN BIOSCIENCE

---

- Plasmas, to date, have played important but limited roles in bioscience.
  - Plasma sterilization
  - Plasma source ion implantation for hardening hip and knee replacements.
  - Modification of surfaces for biocompatibility (in vitro and in vivo)
  - Artificial skin
- The potential for use of “commodity” plasmas for biocompatibility is untapped.



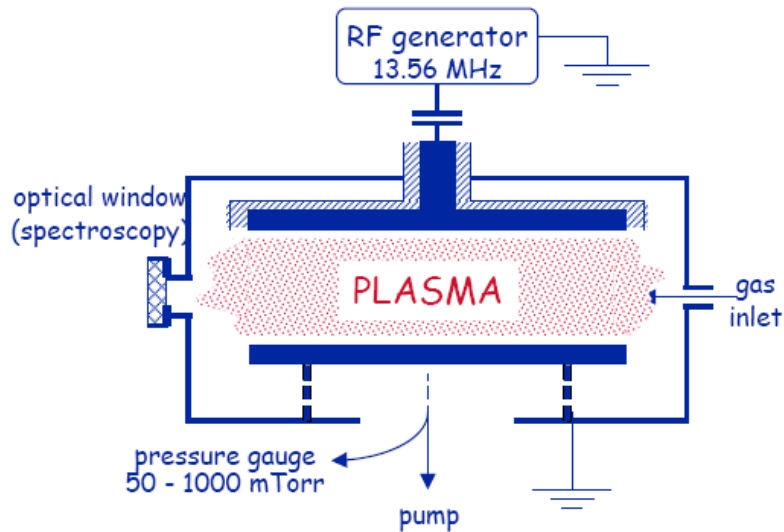
**STERRAD® 200**  
**ASP** ADVANCED STERILIZATION PRODUCTS®  
a *Johnson & Johnson* company  
Division of Ethicon, Inc.

- Low pressure rf H<sub>2</sub>O<sub>2</sub> plasma ([www.sterrad.com](http://www.sterrad.com))

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# Plasma Processes for Cell Adhesion



**INHIBITION**

PEO-like  
coatings

**PROMOTION**

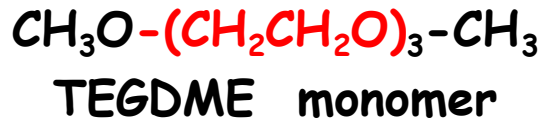
Grafted N-groups  
-COOH functional coatings

pattern

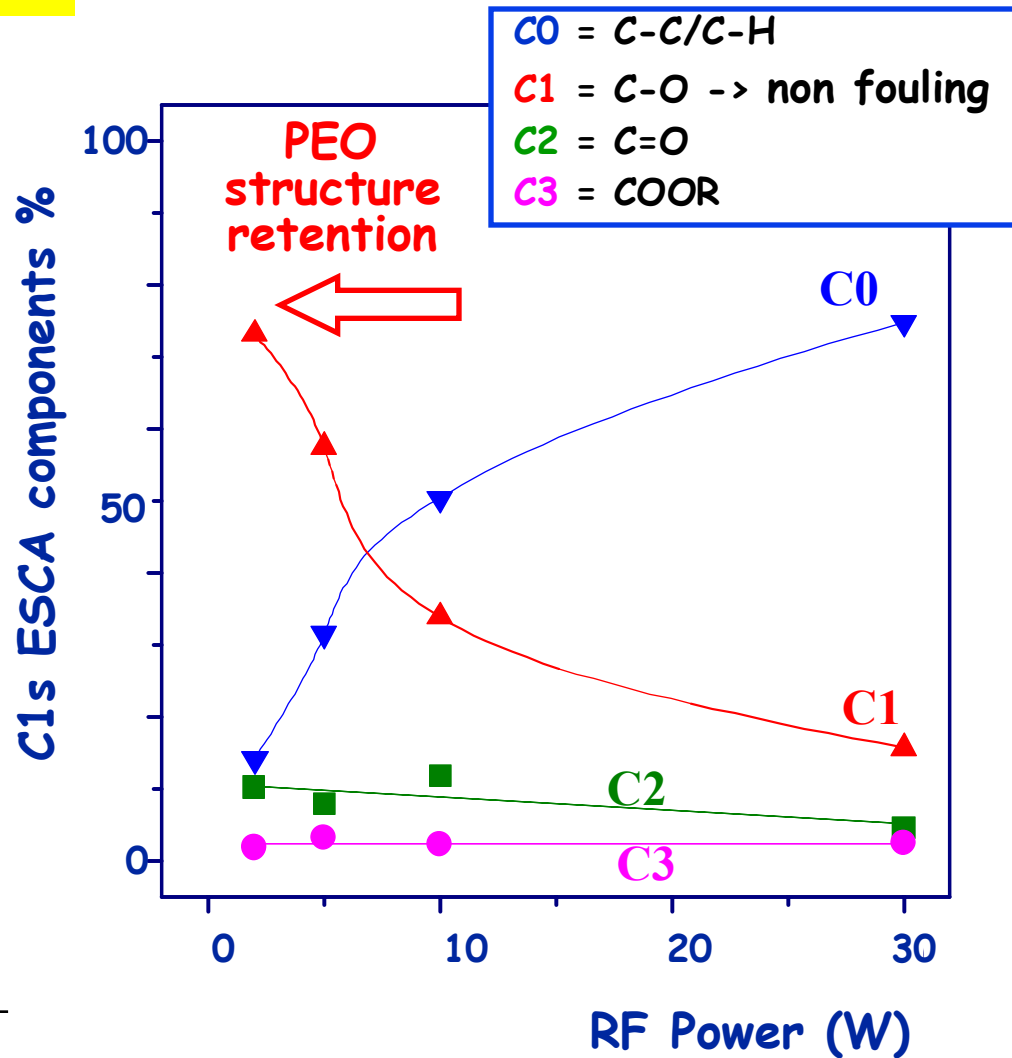
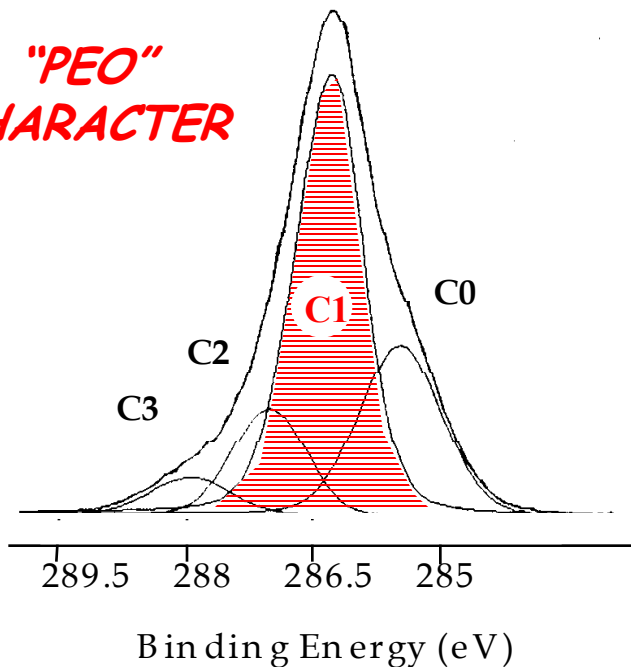
**MICROSTRUCTURED SURFACES**

adhesive zones/ non fouling zones

# XPS MEASUREMENTS



**"PEO"  
CHARACTER**



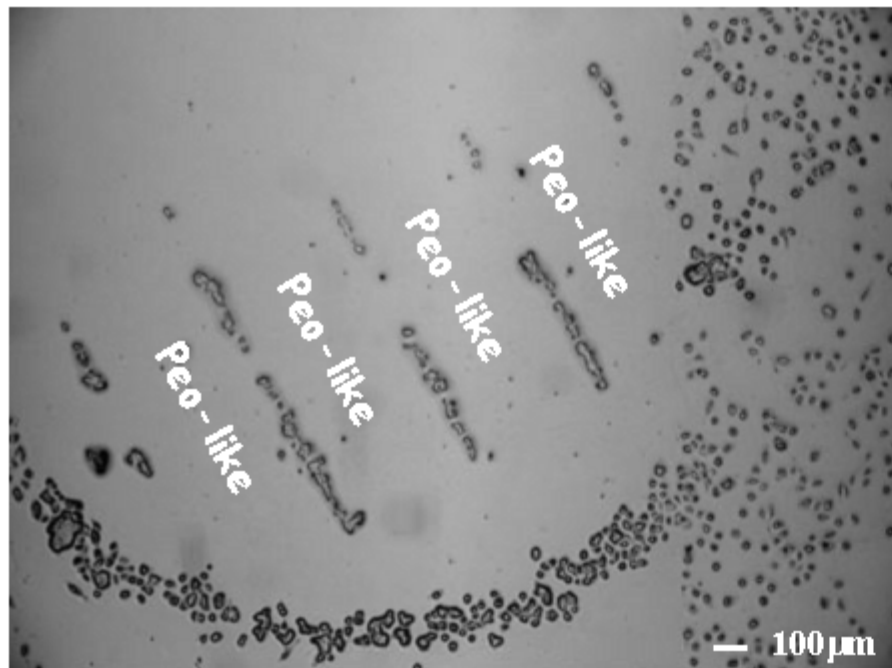




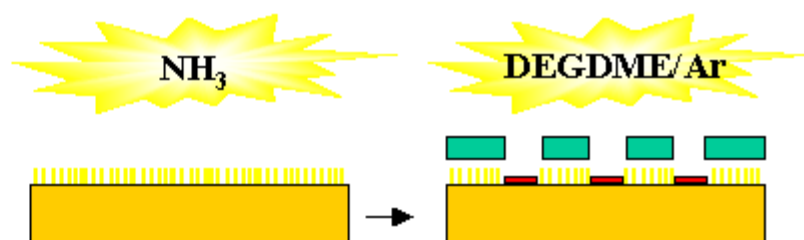
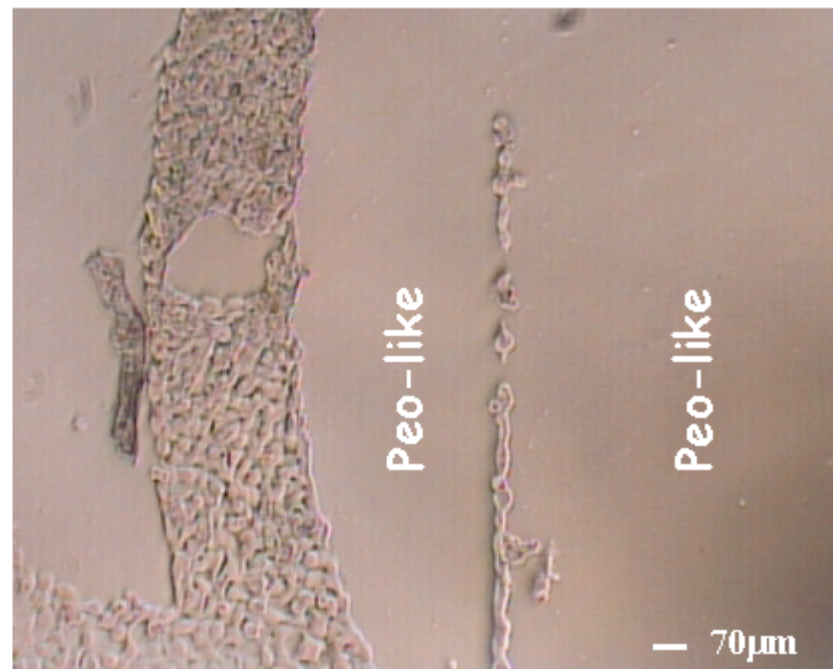
G50P  
holes= 416 $\mu$ m  
bar= 84 $\mu$ m

# NCTC2544 human keratinocytes onto microstructured PS

## PS/PEO-like



## N-groups/PEO-like

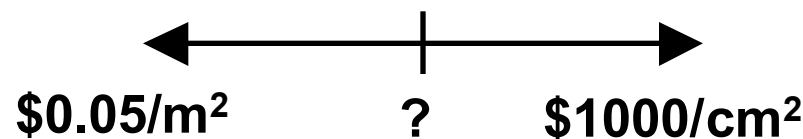


Ref: P. Favia

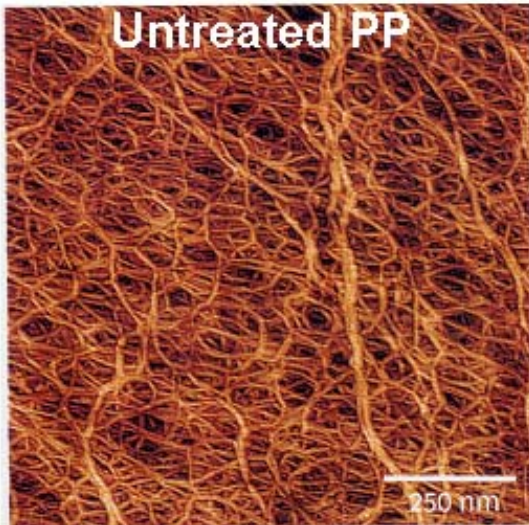
# ATMOSPHERIC PRESSURE PLASMAS: *THE CHALLENGE*

---

- *Controlling functional groups on polymers through fundamental understanding of plasma-solid interactions will enable engineering large area biocompatible surfaces.*
- 10,000 square miles of polymer sheets are treated annually with atmospheric pressure plasmas to achieve specific functionality. Cost: < \$0.05 /m<sup>2</sup>
- Low pressure plasma processing technologies produce biocompatible polymers having similar functionalities. Cost: up to \$100's /cm<sup>2</sup> (\$1000's/cm<sup>2</sup> for artificial skin)
- *Can commodity, atmospheric pressure processing technology be leveraged to produce high value biocompatible films at low cost? The impact on health care would be immeasurable.*



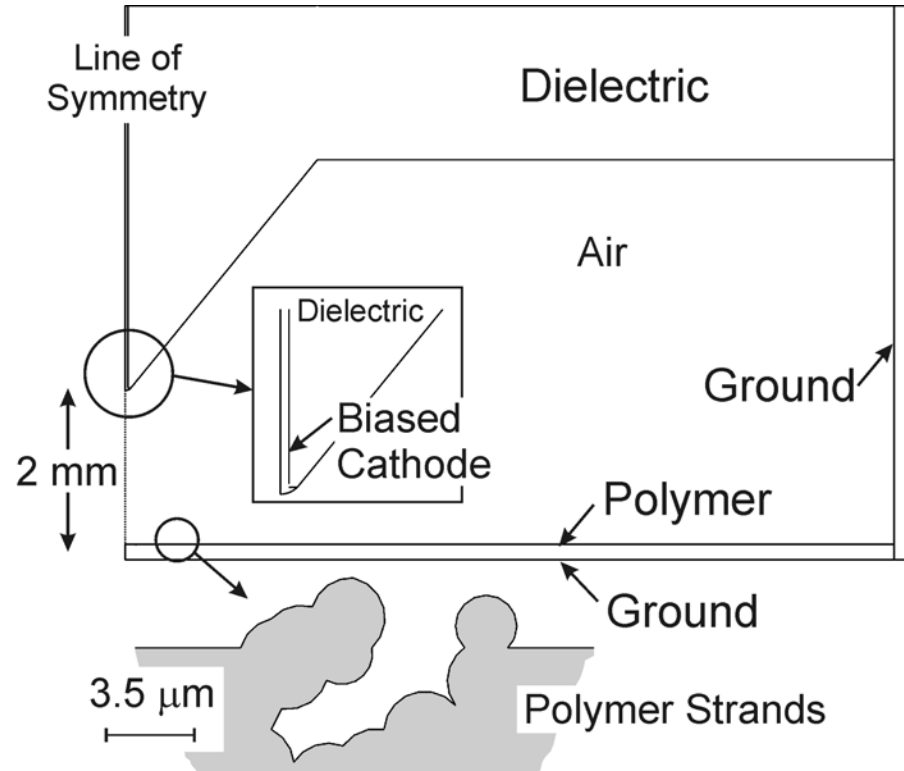
# CAN COMMODITY PROCESSES PRODUCE HIGH VALUE MATERIALS?



- M. Strobel, 3M



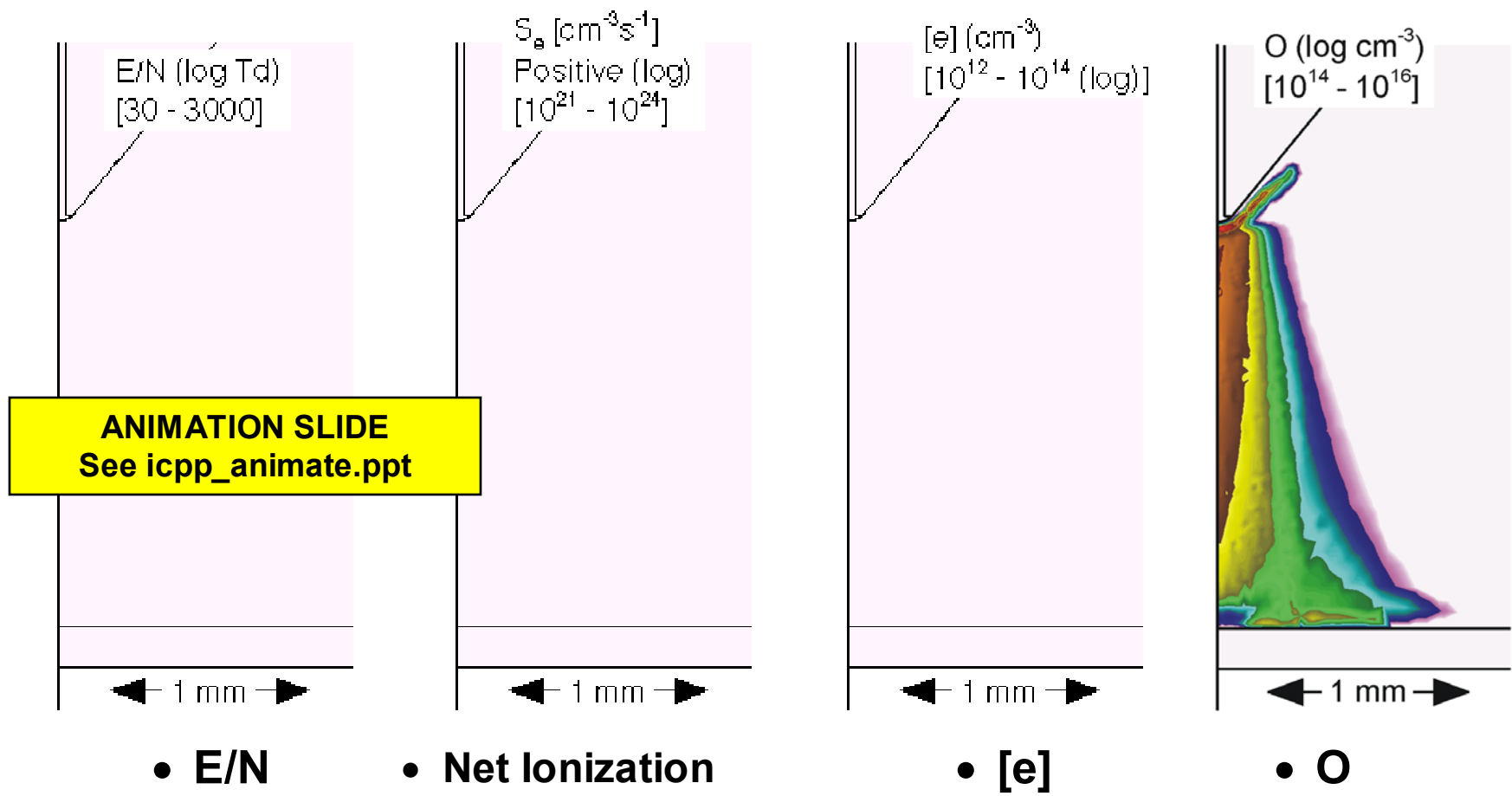
- Tantec, Inc.



- Demonstration: corona-rod, 2 mm gap, 15 kV pulse,  $N_2/O_2/H_2O = 79.5 / 19.5 / 1$ , 1 atm

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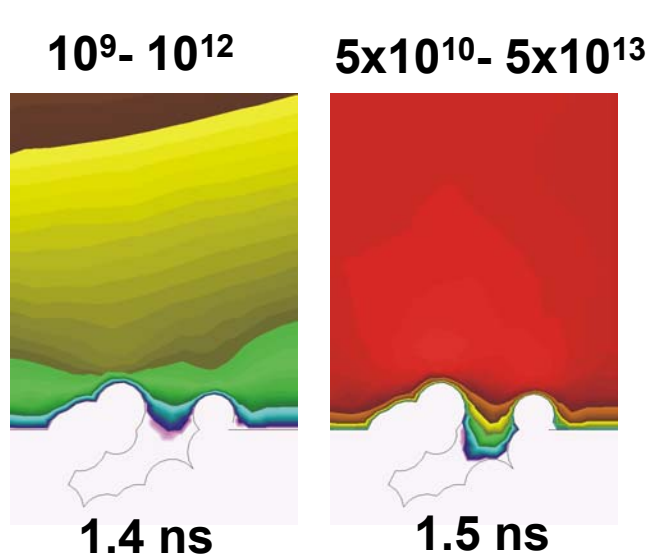
- Development of plasma streamer produces large electric field, electron sources, ionization and radical production.



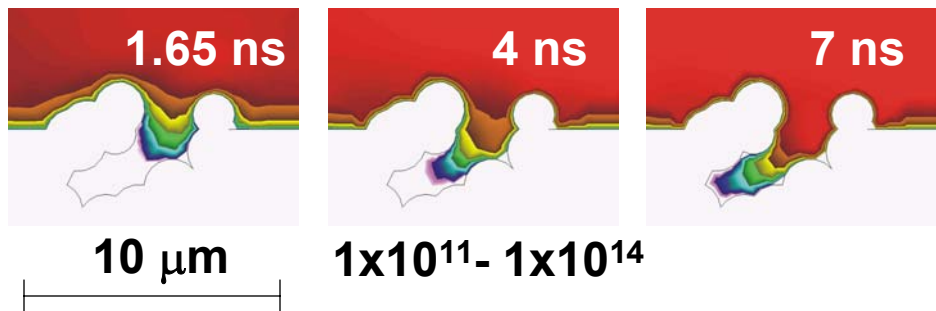
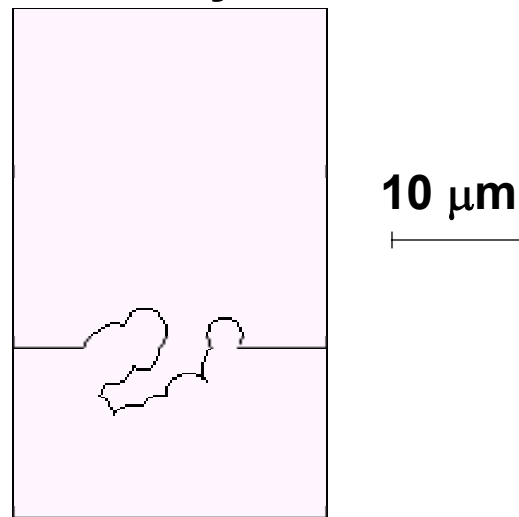
- $\text{N}_2/\text{O}_2/\text{H}_2\text{O} = 79.5 / 19.5 / 1$ , 1 atm, 15 kV, 0-15 ns

MIN  MAX

# SURFACE INTERACTIONS: O RADICALS, IONS



+15 kV cycle



- Positive Ions ( $10^9 - 5 \times 10^{13} \text{ cm}^{-3}$ )
- Ion penetration is ultimately controlled by surface charging.
- O radicals penetrate deeper into the features.

• [O] cm<sup>-3</sup>

ANIMATION SLIDE  
See icpp\_animate.ppt

- 15 kV, 1 atm,  
N<sub>2</sub>/O<sub>2</sub>/H<sub>2</sub>O=79.5/19.5/1

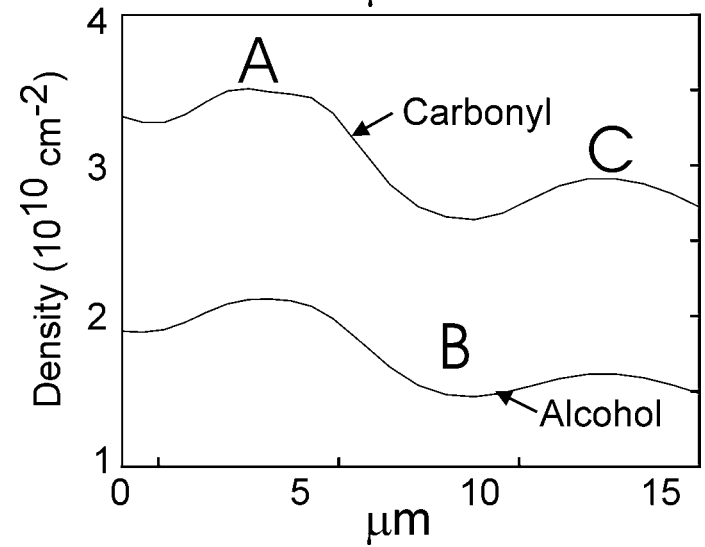
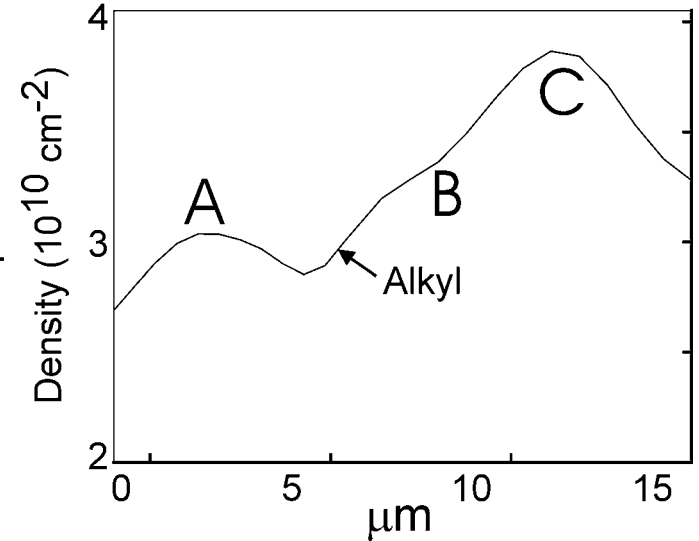
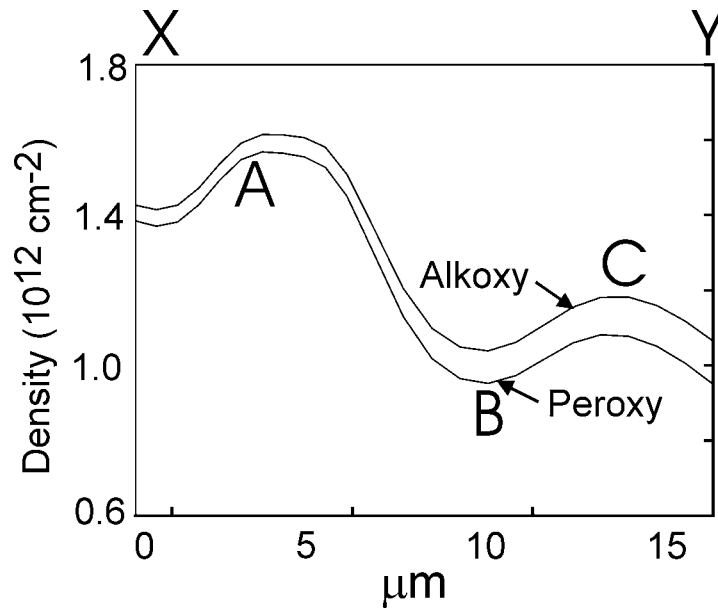
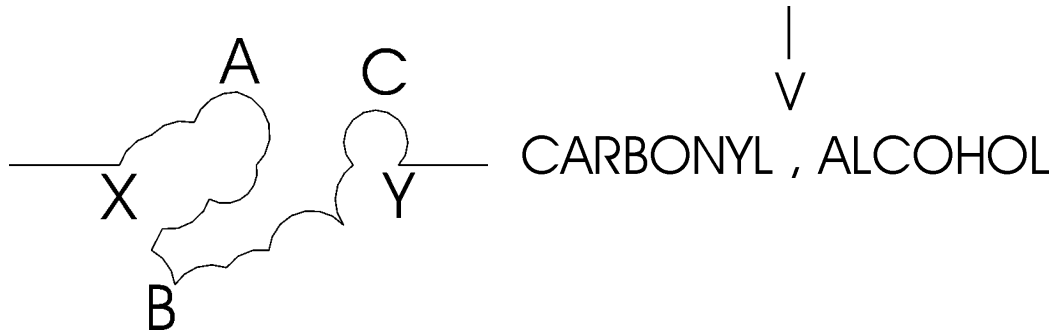


MIN (log scale) MAX

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# FUNCTIONAL GROUP DENSITIES ON POLYPROPYLENE

PP --> ALKYL --> ALKOXY, PEROXY

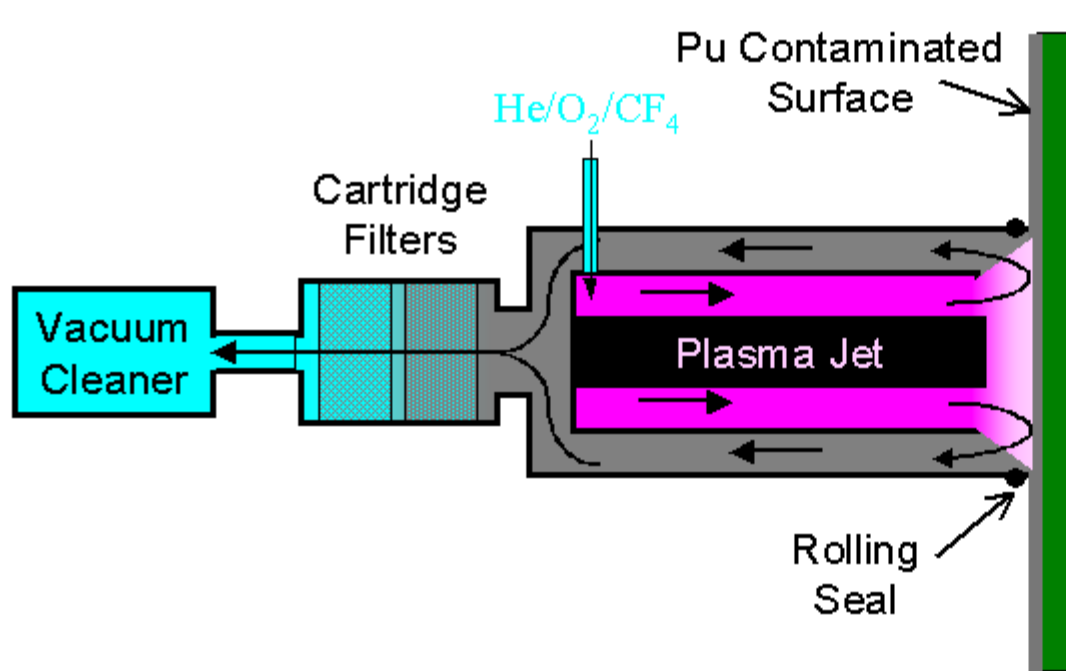


- 1 atm,  $\text{N}_2/\text{O}_2/\text{H}_2\text{O}=79.5/19.5/1$ ,  
1.5 ms, 10 kHz.

***ATMOSPHERIC PRESSURE PLASMAS:  
SURFACES, PHOTONS, FLOW***



# APPJ-based Decontamination

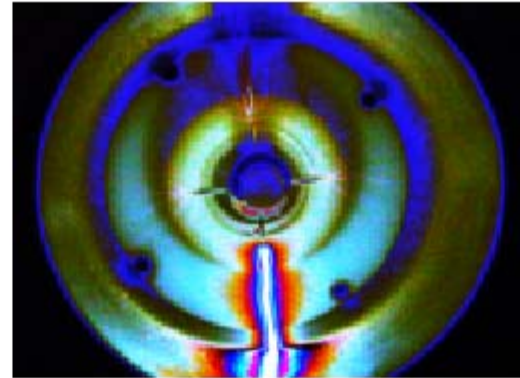
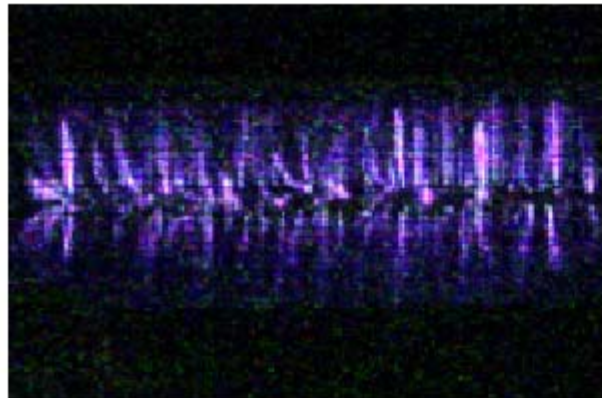


## Decon Benefits:

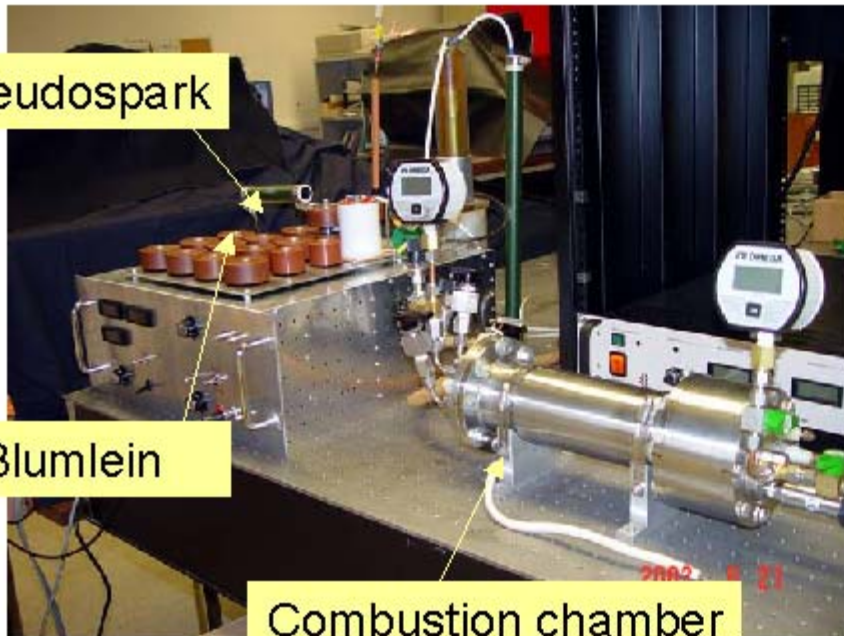
- Innocuous feed gases (He, CF<sub>4</sub>, O<sub>2</sub>)
- Dry - no secondary waste stream
- Actinides potentially recoverable
- Endpoint detection possible

- **Decontamination Concept** ⇒ **Volume Reduction**
- Energetic plasma electrons dissociate CF<sub>4</sub> forming F atoms
- Oxygen reacts with CF<sub>x</sub> molecules to prevent recombination
- Atomic Fluorine etches contamination:  $\text{Pu(s)} + 6\text{F(g)} \Rightarrow \text{PuF}_6\text{(g)}$
- Volatile byproducts (e.g., PuF<sub>6</sub>) captured in adsorbent and HEPA filters
- “Rolling Seal” allows motion while eliminating spread of contamination

# Transient Plasma ignition experiments



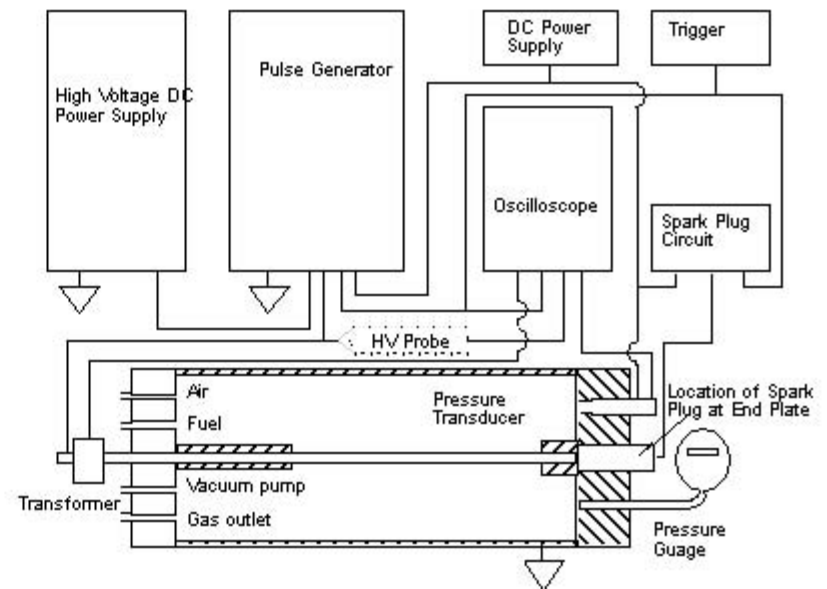
Transient (left)  
vs. Arc (Right)



Pseudospark

Blumlein

Combustion chamber

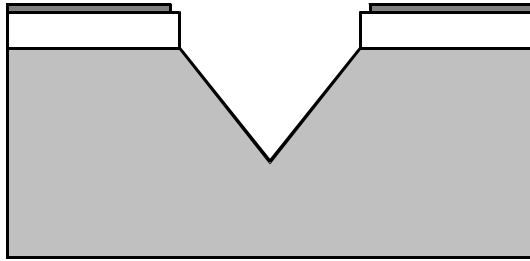


Ref: M. Gundersen

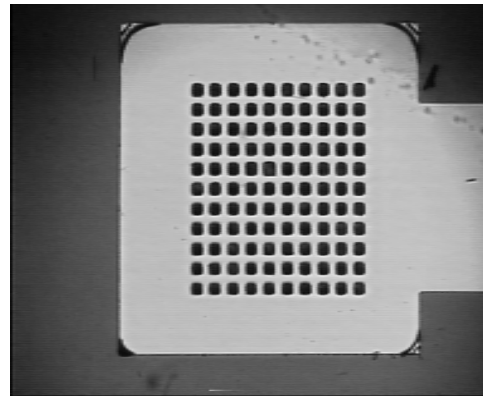
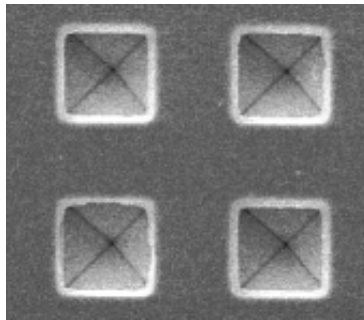
# MICRODISCHARGES: MEMS FABRICATION

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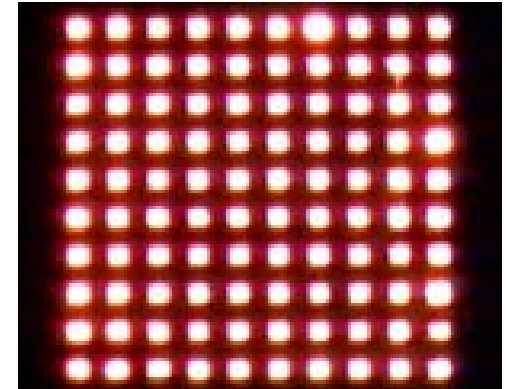
- Microdischarges leverage pd scaling to operate at atmospheric pressure with sizes  $< 10\text{s } \mu\text{m}$  (pd = 6 Torr-cm,  $p=1$  atm,  $d = 65 \mu\text{m}$ )



Inverted Pyramidal Elctrode



$(30 \mu\text{m})^2$  10 X 11 arrays



1200 Torr Ne

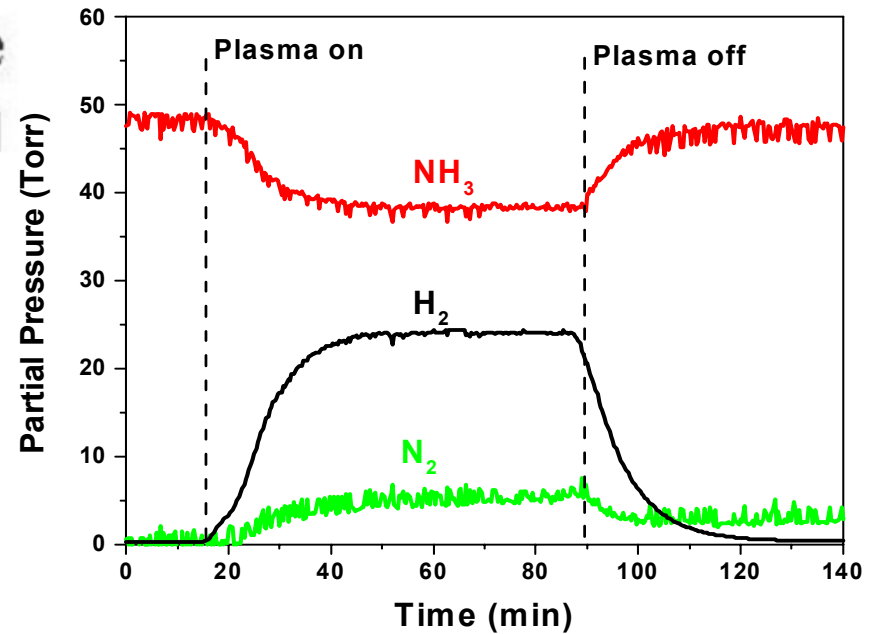
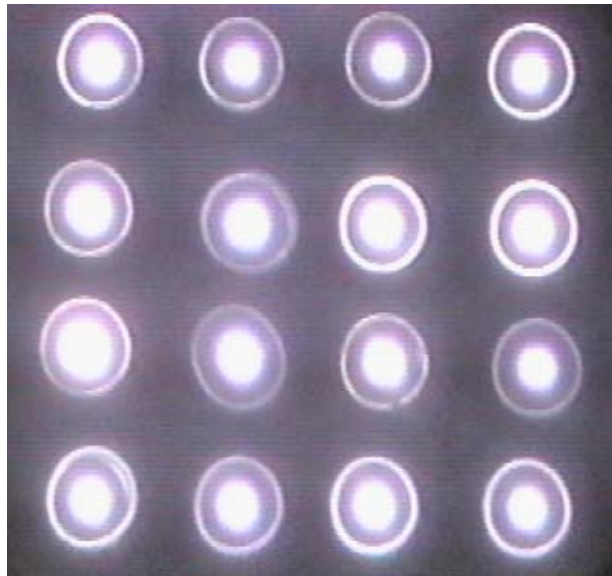
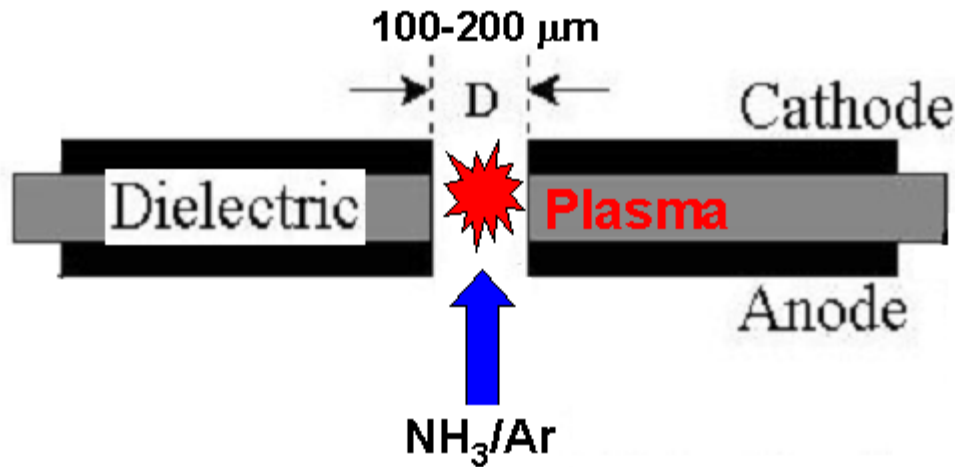
- Using MEMS techniques, arrays of addressable MDs can be fabricated for UV generation, displays, “coherent” photonics with “incoherent” sources.

Ref: J. G. Eden, UIUC

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# In-situ H<sub>2</sub> Generation for Small Scale (i.e. Low Power) Fuel Cells Using a Microhollow Cathode Discharge

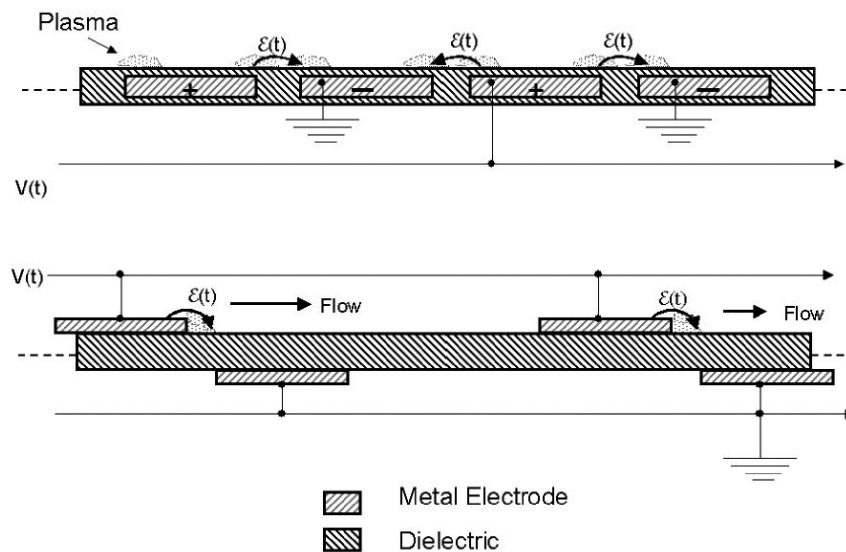


- High throughput is facilitated by microplasma arrays

• Ref: Kurt Becker

# CONTROL OF AERONAUTICAL FLOWS USING PLASMAS

- Charged particles accelerated in electric fields can produce advective motion of gases through momentum transfer.



$$\frac{\text{Force}}{\text{Volume}} = q \left( \sum_i Z_i n_i - n_e \right) E = \rho E = \epsilon_0 E \nabla \cdot E$$

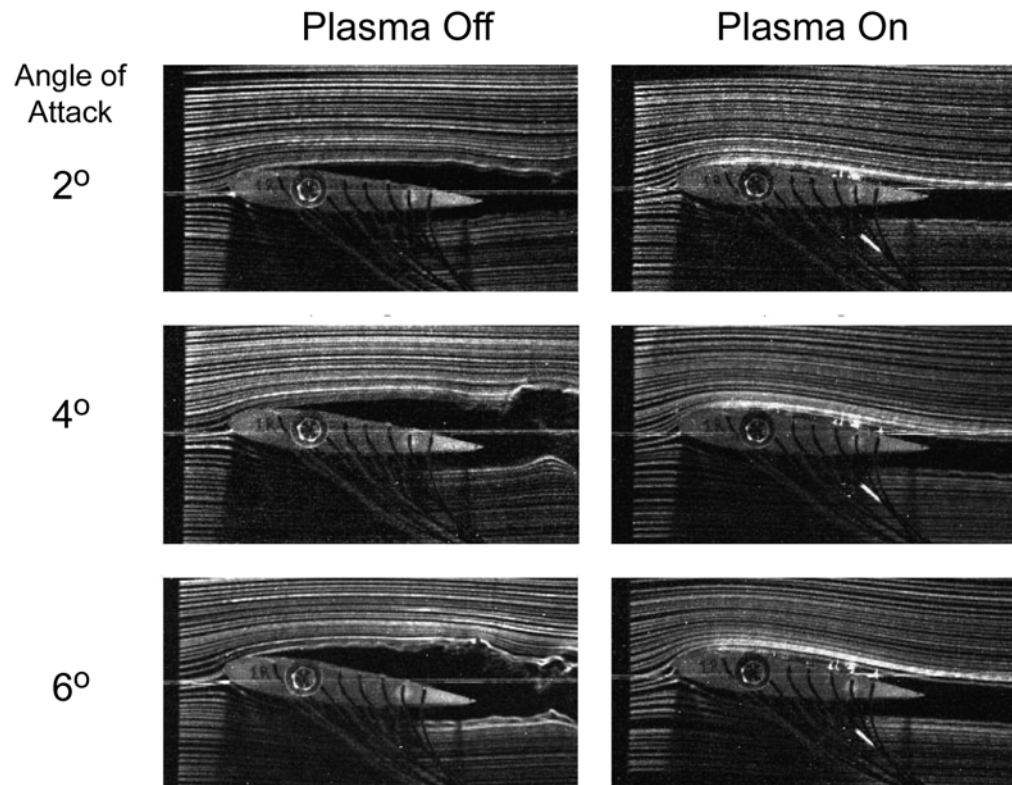
- The flight characteristics of airfoils are sensitive functions of the “adherence” of the boundary layer.
  - Strategically generated plasmas on wings can beneficially and controllably affect lift and steering.
- Example of dielectric barrier discharges for flow control

Ref: R. Roth

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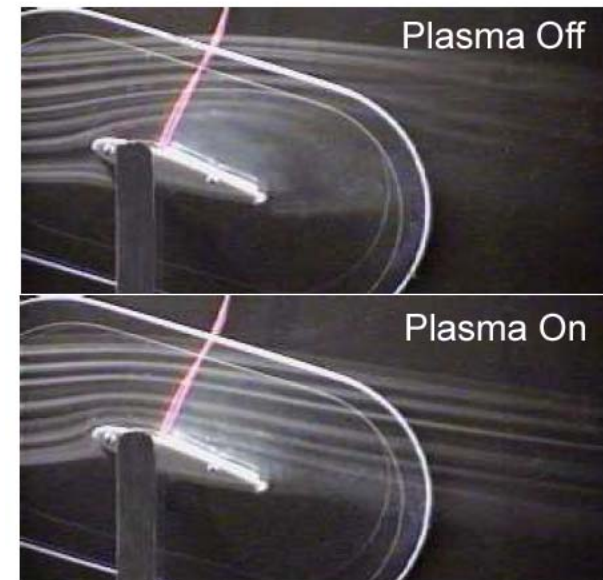
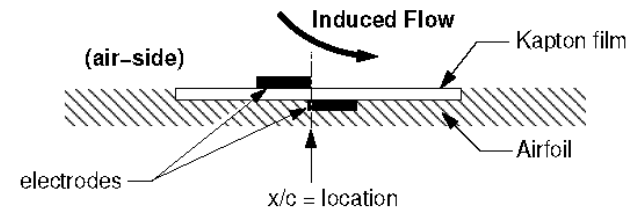


# CONTROL OF AERONAUTICAL FLOWS USING PLASMAS



Ref: R. Roth, Phys. Plasma 10, 2117 (2003)

- A dielectric barrier discharge on the surface of an airfoil prevents separation of the boundary layer.

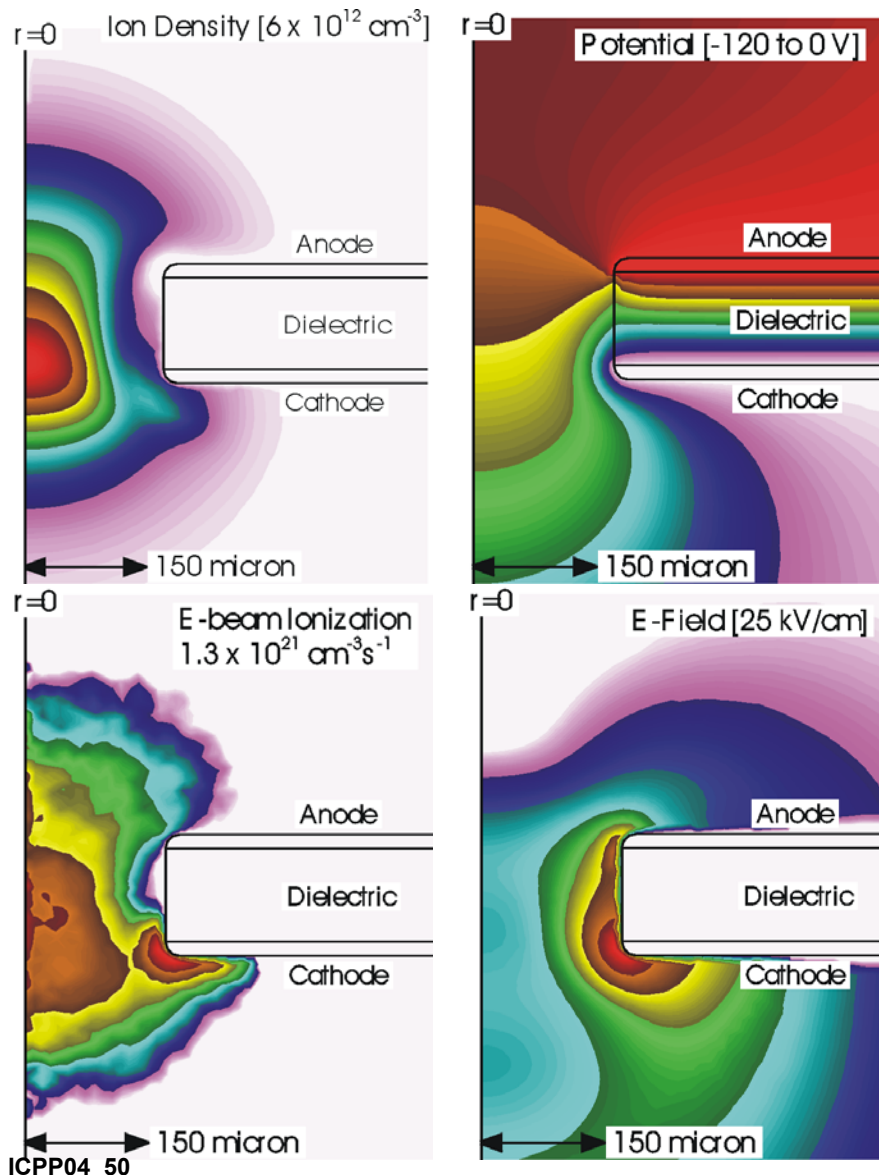


Ref: T. Corke, AIAA 2004-2127

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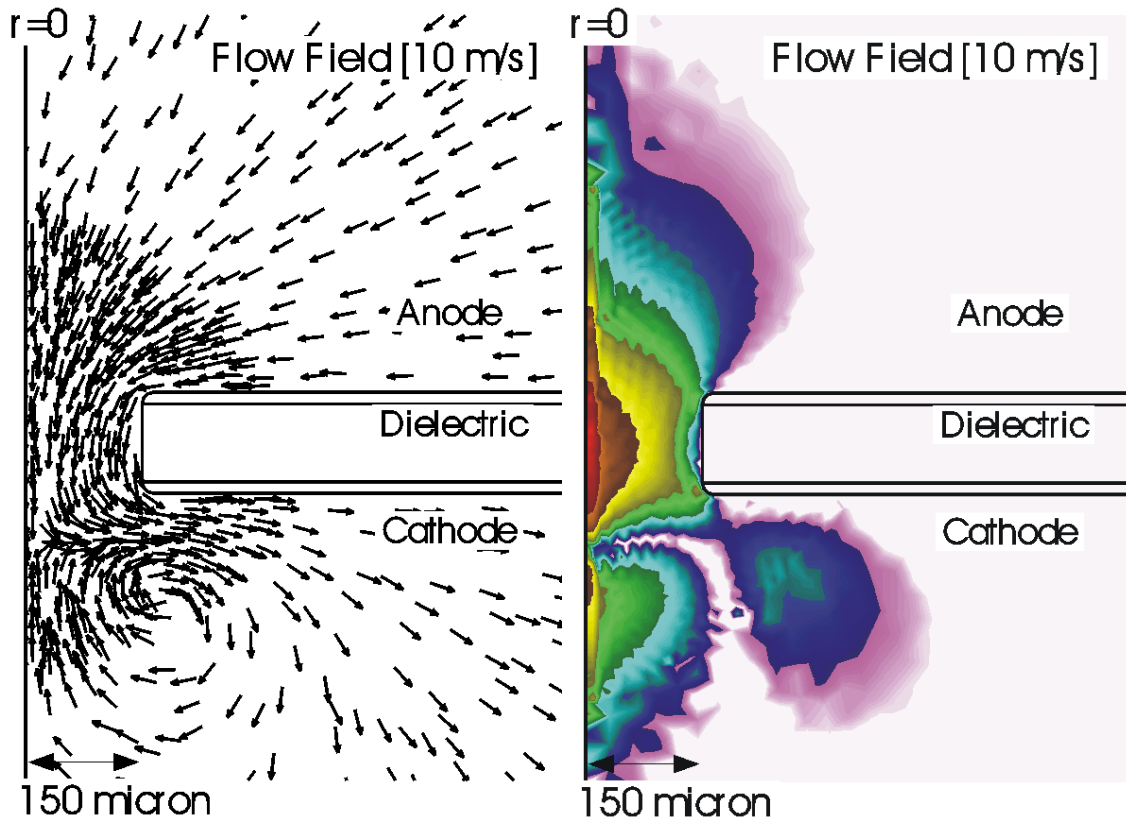
# KEY TO PROGRESS IS LEVERAGING TECHNOLOGIES: MICRODISCHARGE ACTUATORS



- Microdischarges were developed as photon and radial sources.
- Leveraging these technologies enable advances in other areas.
- Arrays of microdischarges may enable control of flow characteristics in “programmable” fashion.
- 600 Torr Ne, 180 V



# GAS PUMPING USING MICRODISCHARGES



- Ion pumping is efficient due to ability to produce large cw ion current densities.
- Flexible arrays enable large areas.
- 600 Torr Ne, 180 V

# ***PLASMAS IN NANOSCIENCE***

# **THE ROLE OF PLASMAS IN NANOSCIENCE**

---

- **Plasma science has been absolutely critical to the development of conventional microelectronics structures.**
- **What will the role of plasma science be in facilitating these advances in truly nanoscale science and technology?**
  - **Atomic layer processing (etch and deposition)**
  - **Plasma aided lithography (trimming)**
  - **Selective activation or functionalization of materials on molecular scales (inanimate and living)**
  - **Self- and directed-assembly**
  - **Commodity production of nanostructures and nanoparticles.**
  - **Plasma physics laboratories**

# SELECTIVE, ALIGNED PLASMA GROWTH OF CARBON NANOTUBES

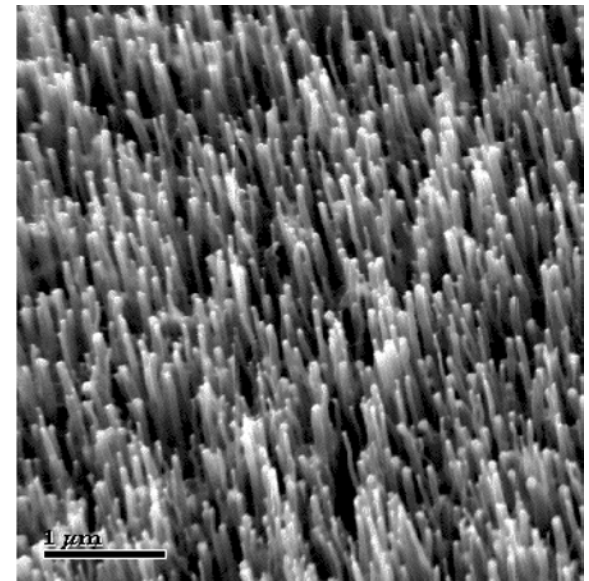
- Aligned CNT growth can be obtained in a low pressure rf and dc plasmas using different feedstocks.
- Catalyst choice and configuration may dominate.



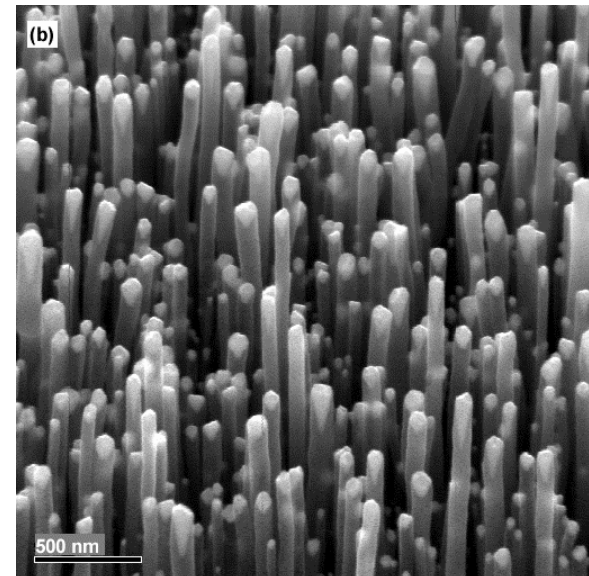
**DC Plasma CVD**

**Ref: B. Cruden**

Cruden et al., J Appl Phys, 12, 363 (2001).

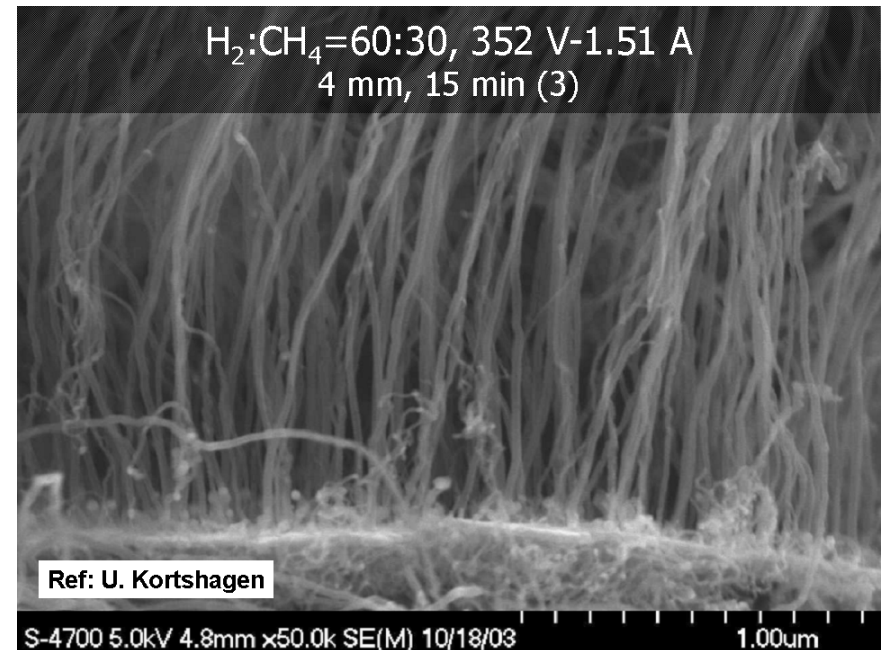
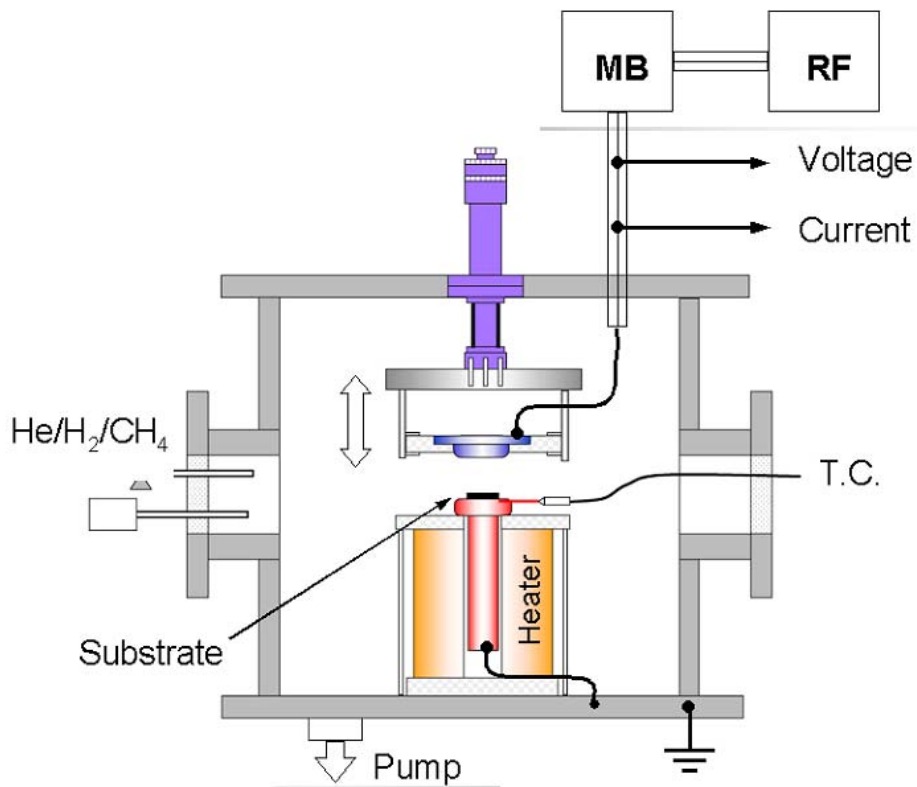


**RF Plasma ( $C_2H_4/NH_3$ )**



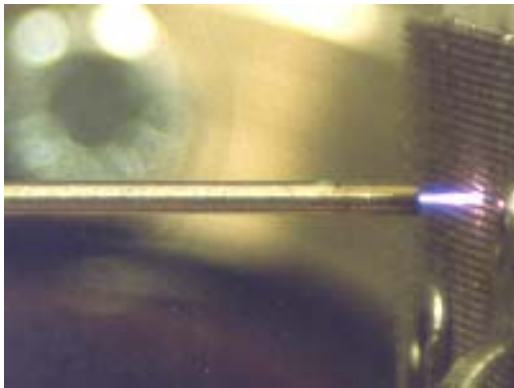
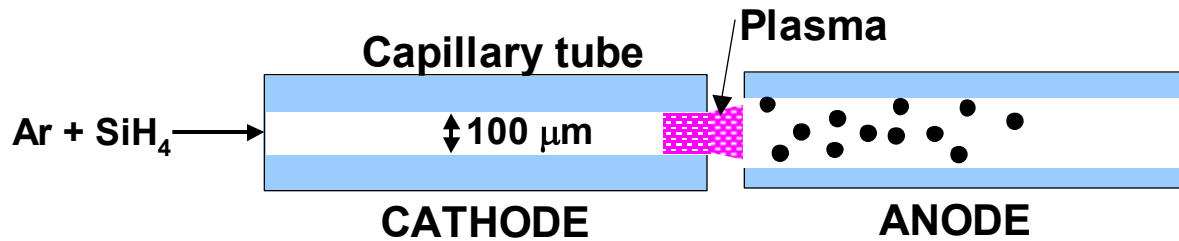
**DC Plasma ( $C_2H_2/NH_3$ )**

# Atmospheric Pressure Plasmas for Carbon Nanotube Deposition



Ref: U. Kortshagen, U. Minnesota

# Microplasmas as Micro-reactors: Nanostructures



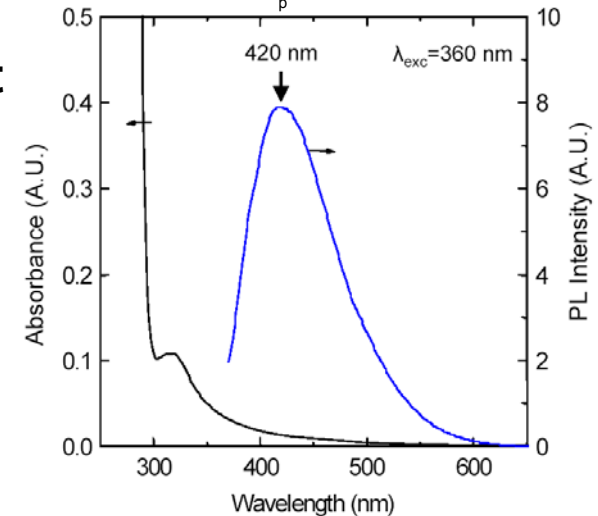
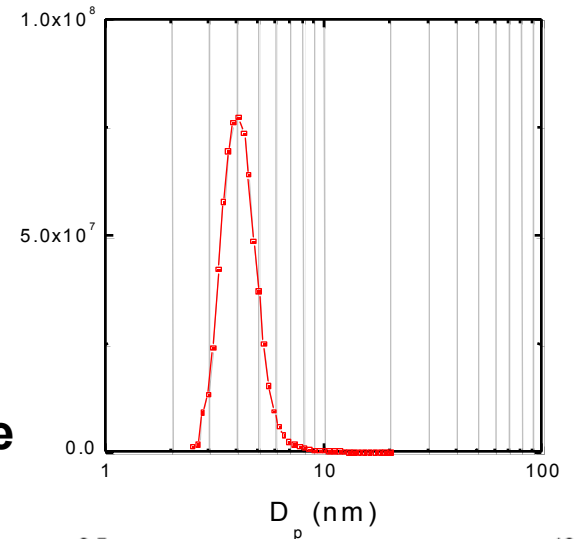
## Typical operating conditions

- 100 sccm Ar in air
- $V_{\text{plasma}} = 450 \text{ VDC}$ ,  $I_{\text{plasma}} = 10.0 \text{ mA}$
- $d_{\text{hole}} = 180 \mu\text{m}$ ,  $L = 2 \text{ mm}$

US Patent No. 6,700,329 – Issued 3/2/04

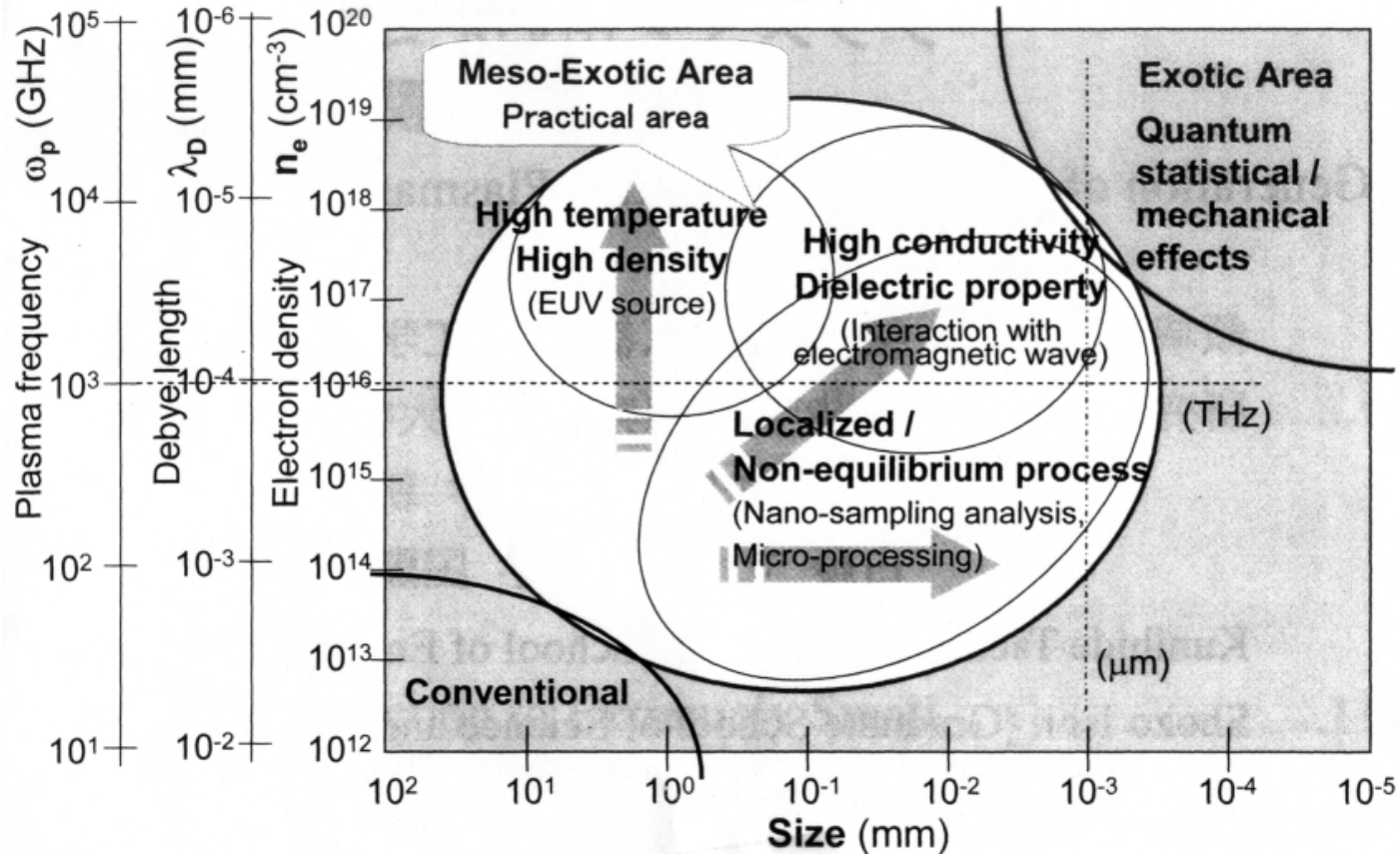
- Short residence time of reactants in plasma zone of microdischarge enables controlled fabrication of fluorescent Si nanoparticles.

- K. P. Giapis, Caltech



# MICRODISCHARGES: MINIATURE PLASMA PHYSICS LABS

- Following microdischarges scaling to  $\geq 10$ s atm,  $[e] > 10^{19} \text{ cm}^{-3}$ ,  $d < 0.1 \mu\text{m}$  provides a cw source of quantum mechanical plasma(?)



- Ref: Annual Progress Report, "Generation of Micro-Scale Reactive Plasmas and Development of Their New Applications" K. Tachibana, Project Leader, March 2004



# CONCLUDING REMARKS

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- **Low temperature, technological plasmas address an array of high technology and commodity applications.**
- **The widest use of low temperature plasmas is production of extremely high value materials (e.g., microelectronics) and low values materials (e.g., polymer functionalization).**
- **The key to advancing the state of the art is improving fundamental understanding while leveraging low cost processes for high value materials. For example,**
  - **Plasma modified polymers for artificial skin**
  - **Microplasma produced nanoparticles**